TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

128-MBIT (16M × 8 BITS/8M × 16 BITS) CMOS FLASH MEMORY

DESCRIPTION

The TC58FVM7T2A/B2A is a 134217728-bit, 3.0-V read-only electrically erasable and programmable flash memory organized as 16777216 words \times 8 bits or as 8388608 words \times 16 bits. The TC58FVM7T2A/B2A features commands for Read, Program and Erase operations to allow easy interfacing with microprocessors. The commands are based on the JEDEC standard. The Program and Erase operations are automatically executed in the chip. The TC58FVM7T2A/B2A also features a Simultaneous Read/Write operation so that data can be read during a Write or Erase operation.

FEATURES

• Power supply voltage

 $V_{DD} = 2.3 \text{ V} \sim 3.6 \text{ V}$

• Operating temperature

 $Ta = -40^{\circ}C \sim 85^{\circ}C$

Organization

 $16M \times 8 \text{ bits/8M} \times 16 \text{ bits}$

- Functions
- Simultaneous Read/Write

Page Read

Auto Program, Auto Page Program

Auto Block Erase, Auto Chip Erase

Fast Program Mode/Acceleration Mode

Program Suspend/Resume

Erase Suspend/Resume

data polling/Toggle bit

block protection, boot block protection

Automatic Sleep, support for hidden ROM area

common flash memory interface (CFI)

Byte/Word Modes

• Block erase architecture

 $8 \times 8 \text{ Kbytes}/255 \times 64 \text{ Kbytes}$

• Boot block architecture

TC58FVM7T2A: top boot block

TC58FVM7B2A: bottom boot block

• Mode control

Compatible with JEDEC standard commands

• Erase/Program cycles

 10^5 cycles typ.

Access Time (Random/Page)

	TC58FVM7T	2A/B2AFT65	TC58FVM7T2A/B2AFT80		
V_{DD}	CL = 30 pF	CL = 100 pF	CL = 30 pF	CL = 100 pF	
2.7~3.6V	65 ns/25 ns	70 ns/30 ns	80 ns/30 ns	85 ns/35 ns	
2.3~3.6V	70 ns/30 ns	75 ns/35 ns	85 ns/35 ns	90 ns/40 ns	

• Power consumption

10 μA (Standby)

15 mA (Program/Erase operation)

55 mA (Random Read operation)

11 mA (Address Increment Read operation)

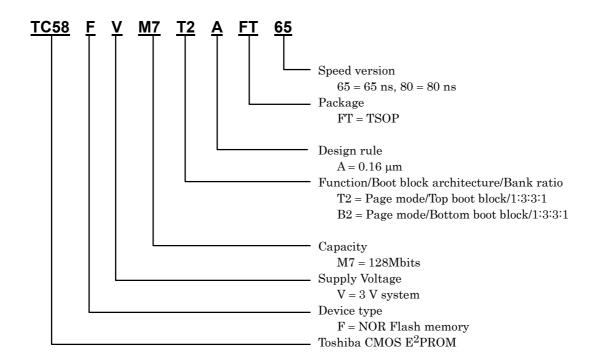
5 mA (Page Read operation)

Package

TSOP I 56-P-1420-0.50A (weight: 0.61g)



Ordering information

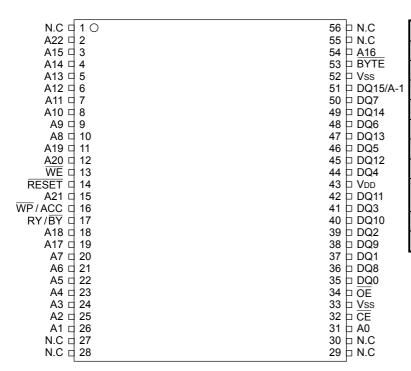


Ordering type	Boot block	Speed version	Package	
TC58FVM7T2AFT65	Тор	65ns	TSOP156-P-1420-0.50	
TC58FVM7B2AFT65	Bottom	OSHS		
TC58FVM7T2AFT80	Тор	85ns	130F130-F-1420-0.30	
TC58FVM7B2AFT80	Bottom	SIICO		



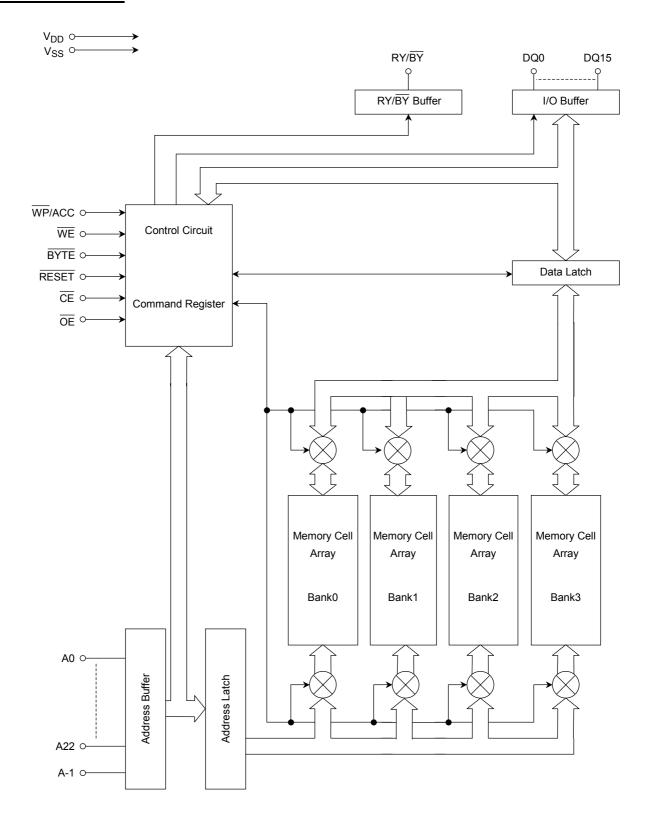
PIN ASSIGNMENT (TOP VIEW)

PIN NAMES



A-1, A0~A22	Address Input
DQ0~DQ15	Data Input/Output
CE	Chip Enable Input
ŌĒ	Output Enable Input
BYTE	Word/Byte Select Input
WE	Write Enable Input
RY/BY	Ready/Busy Output
RESET	Hardware Reset Input
WP/ACC	Write Protect/ Program Acceleration Input
V _{DD}	Power Supply
V _{SS}	Ground

BLOCK DIAGRAM





MODE SELECTION

										DVTE MODE	WODD MODE
		r	r	r	r	•	•	T	T	BYTE MODE	WORD MODE
MODE	CE	ŌĒ	WE	A9	A6	A1	A0	RESET	WP/ACC	DQ0~DQ7 ⁽¹⁾	DQ0~DQ15
Read/Page Read	L	L	Н	A9	A6	A1	A0	Н	*	D _{OUT}	D _{OUT}
ID Read (Manufacturer Code)	L	L	Н	V _{ID}	L	L	┙	Н	*	Code	Code
ID Read (Device Code)	L	L	Н	V _{ID}	L	Ы	Ι	Н	*	Code	Code
Standby	Н	*	*	*	*	*	*	Н	*	High-Z	High-Z
Output Disable	*	Н	Н	*	*	*	*	*	*	High-Z	High-Z
Write	L	Н	(2)	A9	A6	A1	A0	Н	*	D _{IN}	D _{IN}
Block Protect 1	L	V_{ID}	(2) -	V_{ID}	L	Ι	Ы	Н	*	*	*
Block Protect 2	L	Н	Н	*	L	Ι	┙	V _{ID}	*	*	*
Verify Block Protect	L	L	Н	V _{ID}	L	Н	L	Н	*	Code	Code
Temporary Block Unprotect	*	*	*	*	*	*	*	V _{ID}	*	*	*
Hardware Reset/Standby	*	*	*	*	*	*	*	L	*	High-Z	High-Z
Boot Block Protect	*	*	*	*	*	*	*	*	L	*	*

Notes: $* = V_{IH}$ or V_{IL} , $L = V_{IL}$, $H = V_{IH}$

- (1) DQ8~DQ14 are High-Z and DQ15/A-1 is Address Input in Byte Mode. Addresses are A22~A0 in Word Mode ($\overline{BYTE} = V_{IH}$), A22~A-1 in Byte Mode ($\overline{BYTE} = V_{IL}$).
- (2) Pulse input

ID CODE TABLE

CO	DE TYPE	A22~A12	A6	A1	A0	CODE (HEX) ⁽¹⁾
Manufacturer Code		*	L	L	L	0098h
Device Code	TC58FVM7T2A	*	L	L	Н	007Ch
Device Code	TC58FVM7B2A	*	L	L	Н	0082h
Verify Block Protect		BA ⁽²⁾	L	Н	L	Data ⁽³⁾

Notes: $* = V_{IH}$ or V_{IL} , $L = V_{IL}$, $H = V_{IH}$

- (1) DQ8~DQ14 are High-Z and DQ15/A-1 is Address Input in Byte Mode.
- (2) BA: Block Address
- (3) 0001h Protected Block 0000h - Unprotected Block



COMMAND SEQUENCES

COMMAN		BUS WRITE	FIRST BU WRITE CYC			ND BUS CYCLE	THIRD WRITE			TH BUS CYCLE		BUS CYCLE		BUS CYCLE
SEQUENC	E	CYCLES REQ'D	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data
Read/Reset		1	XXXh	F0h										
Dand/Dand	Word	2	555h	A A I-	2AAh	r.c.b	555h	F0h	RA ⁽¹⁾	RD ⁽²⁾				
Read/Reset	Byte	3	AAAh	AAh	555h	55h	AAAh	FUN	KA	RD.				
ID Read	Word	3	555h	AAh	2AAh	55h	BK ⁽³⁾ + 555h	90h	IA ⁽⁴⁾	ID ⁽⁵⁾				
ID Nead	Byte	.	AAAh	7041	555h	0011	BK ⁽³⁾ + AAAh	3011	,,	lib				
Auto-Program	Word	4	555h	AAh	2AAh	55h	555h	A0h	PA ⁽⁶⁾	PD ⁽⁷⁾				
/tato i rogiam	Byte	7	AAAh	7011	555h	0011	AAAh	71011	170					
Auto	Word	11	555h	AAh	2AAh	55h	555h	E6h	PA ⁽⁶⁾	PD ⁽⁷⁾	PA ⁽⁶⁾	PD ⁽⁷⁾	PA ⁽⁶⁾	PD ⁽⁷⁾
PageProgram	Byte	19	AAAh	AAII	555h	3311	AAAh	LOII	FA	FD	FA	FD	FA	FD
Program Suspe	nd	1	BK ⁽³⁾	B0h										
Program Resun	ne	1	вк ⁽³⁾	30h										
Auto Chip	Word	6	555h	AAh	2AAh	55h	555h	80h	555h	AAh	2AAh	55h	555h	10h
Erase	Byte	b	AAAh	AAII	555h	5511	AAAh	OUII	AAAh	AAII	555h	5511	AAAh	1011
Auto Block	Word	0	555h	4 A b	2AAh	EEb	555h	006	555h		2AAh	EEb	BA ⁽⁸⁾	206
Erase	Byte	6	AAAh	AAh	555h	55h	AAAh	80h	AAAh	AAh	555h	55h	BA	30h
Block Erase Su	spend	1	вк ⁽³⁾	B0h										
Block Erase Re	sume	1	BK ⁽³⁾	30h										
Block Protect 2		4	XXXh	60h	BPA ⁽⁹⁾	60h	XXXh	40h	BPA ⁽⁹⁾	BPD ⁽¹⁰⁾				
Verify Block	Word	3	555h	AAh	2AAh	55h	BK ⁽³⁾ + 555h	90h	BPA ⁽⁹⁾	BPD ⁽¹⁰⁾				
Protect	Byte	•	AAAh	70 111	555h	0011	BK ⁽³⁾ + AAAh	0011	BI / \	51 5				
Fast Program	Word	3	555h	AAh	2AAh	55h	555h	20h						
Set	Byte		AAAh	, , , , , ,	555h		AAAh							
Fast Program		2	XXXh	A0h	PA ⁽⁶⁾	PD ⁽⁷⁾								
Fast Program R	eset	2	XXXh	90h	XXXh	F0h ⁽¹³⁾								
Hidden ROM	Word	3	555h	AAh	2AAh	55h	555h	88h						
Mode Entry	Byte	3	AAAh	7711	555h	3311	AAAh	0011						
Hidden ROM	Word	4	555h	AAh	2AAh	55h	555h	A0h	PA ⁽⁶⁾	PD ⁽⁷⁾				
Program	Byte	7	AAAh	AAII	555h	3311	AAAh	Aun	FA	FD				
Hidden ROM	Word	•	555h	n	2AAh	EE.	555h	001-	555h	A A I-	2AAh	554	BA ⁽⁸⁾	201-
Erase	Byte	6	AAAh	AAh	555h	55h	AAAh	80h	AAAh	AAh	555h	55h	BA	30h
Hidden ROM	Word		555h	A A I-	2AAh	EC'-	555h	001-	VVVI	001-				
Mode Exit	Byte	4	AAAh	AAh	555h	55h	AAAh	90h	XXXh	00h				
Query Command	Word Byte	2	$BK^{(3)} + 55h$ $BK^{(3)} + AAh$	98h	CA ⁽¹¹⁾	CD ⁽¹²⁾								

Notes: The system should generate the following address patterns:

Word Mode: 555h or 2AAh on address pins A10~A0 DQ8~DQ15 are ignored in Word Mode.

Byte Mode: AAAh or 555h on address pins A10~A-1

(1) RA: Read Address

(2) RD: Read Data

(3) BK: Bank Address = A22~A20

(4) IA: Bank Address and ID Read Address (A6, A1, A0)
Bank Address = A22~A20
Manufacturer Code = (0, 0, 0)
Device Code = (0, 0, 1)

(5) ID: ID Data

(6) PA: Program Address

(7) PD: Program Data

(8) BA: Block Address = A22~A12

(9) BPA: Block Address and ID Read Address (A6, A1, A0)
Block Address = A22~A12
ID Read Address = (0, 1, 0)

(10) BPD: Verify Data(11) CA: CFI Address(12) CD: CFI Data(13) F0h: 00h is valid too

(Input continuous 8 address from (A0, A1, A2) = (0, 0, 0) to (A0, A1, A2) = (1, 1, 1) in Page program.)



SIMULTANEOUS READ/WRITE OPERATION

The TC58FVM7T2A/B2A features a Simultaneous Read/Write operation. The Simultaneous Read/Write operation enables the device to simultaneously write data to or erase data from a bank while reading data from another bank.

The TC58FVM7T2A/B2A has a total of four banks (16Mbits: 48Mbits: 48Mbits: 16Mbits). Banks can be switched between using the bank addresses (A22~A20). For a description of bank blocks and addresses, please refer to the Block Address Table and Block Size Table.

The Simultaneous Read/Write operation cannot perform multiple operations within a single bank. The table below shows the operation modes in which simultaneous operation can be performed.

Note that during Auto-Program execution or Auto Block Erase operation, the Simultaneous Read/Write operation cannot read data from addresses in the same bank which have not been selected for operation. Data from these addresses can be read using the Program Suspend or Erase Suspend function, however.

SIMULTANEOUS READ/WRITE OPERATION

STATUS OF BANK ON WHICH OPERATION IS BEING PERFORMED	STATUS OF OTHER BANKS		
Read Mode			
ID Read Mode ⁽¹⁾			
Auto-Program Mode			
Auto-Page Program Mode			
Fast Program Mode ⁽²⁾			
Program Suspend Mode	Read Mode		
Auto Block Erase Mode	Read Wode		
Auto Multiple Block Erase Mode ⁽³⁾			
Erase Suspend Mode			
Program during Erase Suspend			
Program Suspend during Erase Suspend			
CFI Mode			

- (1) Only Command Mode is valid.
- (2) Including times when Acceleration Mode is in use.
- (3) If the selected blocks are spread across all nine banks, simultaneous operation cannot be carried out.

OPERATION MODES

In addition to the Read, Write and Erase Modes, the TC58FVM7T2A/B2A features many functions including block protection and data polling. When incorporating the device into a deign, please refer to the timing charts and flowcharts in combination with the description below.

READ MODE (PAGE READ)

To read data from the memory cell array, set the device to Read Mode. In Read Mode the device can perform high-speed random access and Page Read as asynchronous ROM.

The device is automatically set to Read Mode immediately after power-on or on completion of automatic operation. A software reset releases ID Read Mode and the lock state which the device enters if automatic operation ends abnormally, and sets the device to Read Mode. A hardware reset terminates operation of the device and resets it to Read Mode. When reading data without changing the address immediately after power-on, either input a hardware Reset or change $\overline{\text{CE}}$ from H to L.



ID Read Mode

ID Read Mode is used to read the device maker code and device code. The mode is useful in that it allows EPROM programmers to identify the device type automatically.

ID read can be executed in two ways, as follows:

(1) Applying VID to A9

This method is used mainly by EPROM programmers. Applying VID to A9 sets the device to ID Read Mode, outputting the maker code from address 00H and the device code from address 01H. Releasing VID from A9 returns the device to Read Mode. With this method all banks are set to ID Read Mode; thus, simultaneous operation cannot be performed.

(2) Input command sequence

With this method simultaneous operation can be performed. Inputting an ID Read command sets the specified bank to ID Read Mode. Banks are specified by inputting the bank address (BK) in the third Bus Write cycle of the Command cycle. To read an ID code, the bank address as well as the ID read address must be specified (with $\overline{WP}/ACC = VIH$ or VIL). The maker code is output from address BK + 00; the device code is output from address BK + 01. From other banks data are output from the memory cells. Inputting a Reset command releases ID Read Mode and returns the device to Read Mode.

Access time in ID Read Mode is the same as that in Read Mode. For a list of the codes, please refer to the ID Code Table.

Standby Mode

There are two ways to put the device into Standby Mode.

(1) Control using \overline{CE} and \overline{RESET}

With the device in Read Mode, input $V_{DD} \pm 0.3 \ V$ to CE and RESET. The device will enter Standby Mode and the current will be reduced to the standby current (IDDS1). However, if the device is in the process of performing simultaneous operation, the device will not enter Standby Mode but will instead cause the operating current to flow.

(2) Control using \overline{RESET} only

With the device in Read Mode, input $V_{SS} \pm 0.3~V$ to \overline{RESET} . The device will enter Standby Mode and the current will be reduced to the standby current (IDDS1). Even if the device is in the process of performing simultaneous operation, this method will terminate the current operation and set the device to Standby Mode. This is a hardware reset and is described later.

In Standby Mode DQ is put in High-Impedance state.

Auto-Sleep Mode

This function suppresses power dissipation during reading. If the address input does not change for 150 ns, the device will automatically enter Sleep Mode and the current will be reduced to the standby current (IDDS2). However, if the device is in the process of performing simultaneous operation, the device will not enter Standby Mode but will instead cause the operating current to flow. Because the output data is latched, data is output in Sleep Mode. When the address is changed, Sleep Mode is automatically released, and data from the new address is output.

Output Disable Mode

Inputting VIH to $\overline{\rm OE}$ disables output from the device and sets DQ to High-Impedance.



Command Write

The TC58FVM7T2A/B2A uses the standard JEDEC control commands for a single-power supply E^2PROM . A Command Write is executed by inputting the address and data into the Command Register. The command is written by inputting a pulse to \overline{WE} with $\overline{CE} = VIL$ and $\overline{OE} = VIH$ (\overline{WE} control). The command can also be written by inputting a pulse to \overline{CE} with $\overline{WE} = VIL$ (\overline{CE} control). The address is latched on the falling edge of either \overline{WE} or \overline{CE} . The data is latched on the rising edge of either \overline{WE} or \overline{CE} . DQ0~DQ7 are valid for data input and DQ8~DQ15 are ignored.

To abort input of the command sequence use the Reset command. The device will reset the Command Register and enter Read Mode. If an undefined command is input, the Command Register will be reset and the device will enter Read Mode.

Software Reset

Apply a software reset by inputting a Read/Reset command. A software reset returns the device from ID Read Mode or CFI Mode to Read Mode, releases the lock state if automatic operation has ended abnormally, and clears the Command Register.

Hardware Reset

A hardware reset initializes the device and sets it to Read Mode. When a pulse is input to $\overline{\text{RESET}}$ for trp, the device abandons the operation which is in progress and enters Read Mode after tready. Note that if a hardware reset is applied during data overwriting, such as a Write or Erase operation, data at the address or block being written to at the time of the reset will become undefined.

After a hardware reset the device enters Read Mode if $\overline{RESET} = VIH$ or Standby Mode if $\overline{RESET} = VIL$. The DQ pins are High-Impedance when $\overline{RESET} = VIL$. After the device has entered Read Mode, Read operations and input of any command are allowed.

Comparison between Software Reset and Hardware Reset

ACTION	SOFTWARE RESET	HARDWARE RESET
Releases ID Read Mode or CFI Mode.	True	True
Clears the Command Register.	True	True
Releases the lock state if automatic operation has ended abnormally.	True	True
Stops any automatic operation which is in progress.	False	True
Stops any operation other than the above and returns the device to Read Mode.	False	True

BYTE/Word Mode

 \overline{BYTE} is used select Word Mode (16 bits) or Byte Mode (8 bits) for the TC58FVM7T2A/B2A. If VIH is input to \overline{BYTE} , the device will operate in Word Mode. Read data or write commands using DQ0~DQ15. When VIL is input to \overline{BYTE} , read data or write commands using DQ0~DQ7. DQ15/A-1 is used as the lowest address. DQ8~DQ14 will become High-Impedance.



Auto-Program Mode

The TC58FVM7T2A/B2A can be programmed in either byte or word units. Auto-Program Mode is set using the Program command. The program address is latched on the falling edge of the $\overline{\rm WE}$ signal and data is latched on the rising edge of the fourth Bus Write cycle (with $\overline{\rm WE}$ control). Auto programming starts on the rising edge of the $\overline{\rm WE}$ signal in the fourth Bus Write cycle. The Program and Program Verify commands are automatically executed by the chip. The device status during programming is indicated by the Hardware Sequence flag. To read the Hardware Sequence flag, specify the address to which the Write is being performed.

During Auto Program execution, a command sequence for the bank on which execution is being performed cannot be accepted. To terminate execution, use a hardware reset. Note that if the Auto-Program operation is terminated in this manner, the data written so far is invalid.

Any attempt to program a protected block is ignored. In this case the device enters Read Mode 3 μ s after the rising edge of the \overline{WE} signal in the fourth Bus Write cycle.

If an Auto-Program operation fails, the device remains in the programming state and does not automatically return to Read Mode. The device status is indicated by the Hardware Sequence flag. Either a Reset command or a hardware reset is required to return the device to Read Mode after a failure. If a programming operation fails, the block which contains the address to which data could not be programmed should not be used.

The device allows 0s to be programmed into memory cells which contain a 1. 1s cannot be programmed into cells which contain 0s. If this is attempted, execution of Auto Program will fail. This is a user error, not a device error. A cell containing 0 must be erased in order to set it to 1.

Auto-Page Program Mode

Auto-Page Program is a function which enables to simultaneously program 8words or 16bytes data. In this mode Program time for 128M bit is less than 60% compare with Auto program mode. In word mode, input page program command during first bus write cycle to third bus write cycle. Input program data and address of (A0, A1, A2) = (0, 0, 0) in forth bus write cycle. Input increment address and program data during fifth bus write cycle to eleventh bus write cycle. After input eleventh bus write cycle, page program operation start. In byte mode, input increment address and program data of $(A-1, A0, A1, A2) = (0, 0, 0, 0) \cdots (A-1, A0, A1, A2) = (1, 1, 1, 1)$ during fifth bus write cycle to nineteenth bus write cycle.

Fast Program Mode

Fast Program is a function which enables execution of the command sequence for the Auto Program to be completed in two cycles. In this mode the first two cycles of the command sequence, which normally requires four cycles, are omitted. Writing is performed in the remaining two cycles. To execute Fast Program, input the Fast Program command. Write in this mode uses the Fast Program command but operation is the same at that for ordinary Auto-Program. The status of the device is indicated by the Hardware Sequence flag and read operations can be performed as usual. To exit this mode, the Fast Program Reset command must be input. When the command is input, the device will return to Read Mode.

Acceleration Mode

The TC58FVM7T2A/B2A features Acceleration Mode which allows write time to be reduced. Applying Vacc to $\overline{\text{WP}}$ or ACC automatically sets the device to Acceleration Mode. In Acceleration Mode, Block Protect Mode changes to Temporary Block Unprotect Mode. Write Mode changes to Fast Program Mode. Modes are switched by the $\overline{\text{WP}}/\text{ACC}$ signal; thus, there is no need for a Temporary Block Unprotect operation or to set or reset Fast Program Mode. Operation of Write is the same as in Auto-Program Mode. Removing Vacc from $\overline{\text{WP}}/\text{ACC}$ terminates Acceleration Mode.



Program Suspend/Resume Mode

Program Suspend is used to enable Data Read by suspending the Write operation. The device accepts a Program Suspend command in Write Mode (including Write operations performed during Erase Suspend) but ignores the command in other modes. When the command is input, the address of the bank on which Write is being performed must be specified. After input of the command, the device will enter Program Suspend Read Mode after tSUSP.

During Program Suspend, Cell Data Read, ID Read and CFI Data Read can be performed. When Data Write is suspended, the address to which Write was being performed becomes undefined. ID Read and CFI Data Read are the same as usual.

After completion of Program Suspend input a Program Resume command to return to Write Mode. When inputting the command, specify the address of the bank on which Write is being performed. If the ID Read or CFI Data Read functions is being used, abort the function before inputting the Resume command. On receiving the Resume command, the device returns to Write Mode and resumes outputting the Hardware Sequence flag for the bank to which data is being written.

Program Suspend can be run in Fast Program Mode or Acceleration Mode. However, note that when running Program Suspend in Acceleration Mode, VACC must not be released.

Auto Chip Erase Mode

The Auto Chip Erase Mode is set using the Chip Erase command. An Auto Chip Erase operation starts on the rising edge of $\overline{\text{WE}}$ in the sixth bus cycle. All memory cells are automatically preprogrammed to 0, erased and verified as erased by the chip. The device status is indicated by the Hardware Sequence flag.

Command input is ignored during an Auto Chip Erase. A hardware reset can interrupt an Auto Chip Erase operation. If an Auto Chip Erase operation is interrupted, it cannot be completed correctly. Hence an additional Erase operation must be performed.

Any attempt to erase a protected block is ignored. If all blocks are protected, the Auto Erase operation will not be executed and the device will enter Read mode 400 μs after the rising edge of the \overline{WE} signal in the sixth bus cycle.

If an Auto Chip Erase operation fails, the device will remain in the erasing state and will not return to Read Mode. The device status is indicated by the Hardware Sequence flag. Either a Reset command or a hardware reset is required to return the device to Read Mode after a failure.

In this case it cannot be ascertained which block the failure occurred in. Either abandon use of the device altogether, or perform a Block Erase on each block, identify the failed block, and stop using it. The host processor must take measures to prevent subsequent use of the failed block.



Auto Block Erase/Auto Multi-Block Erase Modes

The Auto Block Erase Mode and Auto Multi-Block Erase Mode are set using the Block Erase command. The block address is latched on the falling edge of the \overline{WE} signal in the sixth bus cycle. The block erase starts as soon as the Erase Hold Time (tbeh) has elapsed after the rising edge of the \overline{WE} signal. When multiple blocks are erased, the sixth Bus Write cycle is repeated with each block address and Auto Block Erase command being input within the Erase Hold Time (this constitutes an Auto Multi-Block Erase operation). If a command other than an Auto Block Erase command or Erase Suspend command is input during the Erase Hold Time, the device will reset the Command Register and enter Read Mode. The Erase Hold Time restarts on each successive rising edge of \overline{WE} . Once operation starts, all memory cells in the selected block are automatically preprogrammed to 0, erased and verified as erased by the chip. The device status is indicated by the setting of the Hardware Sequence flag. When the Hardware Sequence flag is read, the addresses of the blocks on which auto-erase operation is being performed must be specified. If the selected blocks are spread across all nine banks, simultaneous operation cannot be carried out.

All commands (except Erase Suspend) are ignored during an Auto Block Erase or Auto Multi-Block Erase operation. Either operation can be aborted using a Hardware Reset. If an auto-erase operation is interrupted, it cannot be completed correctly; therefore, a further erase operation is necessary to complete the erasing.

Any attempt to erase a protected block is ignored. If all the selected blocks are protected, the auto-erase operation is not executed and the device returns to Read Mode 400 μs after the rising edge of the \overline{WE} signal in the last bus cycle.

If an auto-erase operation fails, the device remains in Erasing state and does not return to Read Mode. The device status is indicated by the Hardware Sequence flag. After a failure either a Reset command or a Hardware Reset is required to return the device to Read Mode. If multiple blocks are selected, it will not be possible to ascertain the block in which the failure occurred. In this case either abandon use of the device altogether, or perform a Block Erase on each block, identify the failed block, and stop using it. The host processor must take measures to prevent subsequent use of the failed block.

Erase Suspend/Erase Resume Modes

Erase Suspend Mode suspends Auto Block Erase and reads data from or writes data to an unselected block. The Erase Suspend command is allowed during an auto block erase operation but is ignored in all other oreration modes. When the command is input, the address of the bank on which Erase is being performed must be specified.

In Erase Suspend Mode only a Read, Program or Resume command can be accepted. If an Erase Suspend command is input during an Auto Block Erase, the device will enter Erase Suspend Read Mode after tsuse. The device status (Erase Suspend Read Mode) can be verified by checking the Hardware Sequence flag. If data is read consecutively from the block selected for Auto Block Erase, the DQ2 output will toggle and the DQ6 output will stop toggling and RY/\overline{BY} will be set to High-Impedance.

Inputting a Write command during an Erase Suspend enables a Write to be performed to a block which has not been selected for the Auto Block Erase. Data is written in the usual manner.

To resume the Auto Block Erase, input an Erase Resume command. On input of the command, the address of the bank on which the Write was being performed must be specified. On receiving an Erase Resume command, the device returns to the state it was in when the Erase Suspend command was input. If an Erase Suspend command is input during the Erase Hold Time, the device will return to the state it was in at the start of the Erase Hold Time. At this time more blocks can be specified for erasing. If an Erase Resume command is input during an Auto Block Erase, Erase resumes. At this time toggle output of DQ6 resumes and 0 is output on RY/\overline{BY} .



BLOCK PROTECTION

Block Protection is a function for disabling writing and erasing specific blocks. Block protection can be carried out in two ways: by supplying a high voltage (V_{ID}) to the device (see Block protection 1) or by supplying a high voltage and a command sequence (see Block protection 2).

(1) Block protection 1

Specify a device block address and make the following signal settings A9 = OE = VID, A1 = VIH and CE = A0 = A6 = VIL. Now when a pulse is input to \overline{WE} for tPPLH, the device will start to write to the block protection circuit. Block protection can be verified using the Verify Block Protect command. Inputting VIL on \overline{OE} sets the device to Verify Mode. 01H is output if the block is protected and 00H is output if the block is unprotected. If block protection was unsuccessful, the operation must be repeated. Releasing VID from A9 and \overline{OE} terminates this mode.

(2) Block protection 2

Applying VID to \overline{RESET} and inputting the Block Protect 2 command also performs block protection. The first cycle of the command sequence is the Set-up command. In the second cycle, the Block Protect command is input, in which a block address and A1 = VIH and A0 = A6 = VIL are input. Now the device writes to the block protection circuit. There is a wait of tPPLH until this write is completed; however, no intervention is necessary during this time. In the third cycle the Verify Block Protect command is input. This command verifies the write to the block protection circuit. Read is performed in the fourth cycle. If the protection operation is complete, 01H is output. If a value other than 01H is output, block protection is not complete and the Block Protect command must be input again. Removing the VID input from \overline{RESET} exits this mode.

Temporary Block Unprotection

The TC58FVM7T2A/B2A has a temporary block unprotection feature which disables block protection for all protected blocks. Unprotection is enabled by applying VID to the \overline{RESET} pin. Now Write and Erase operations can be performed on all blocks except the boot blocks which have been protected by the Boot Block Protect operation. The device returns to its previous state when VID is removed from the \overline{RESET} pin. That is, previously protected blocks will be protected again.

Verify Block Protect

The Verify Block Protect command is used to ascertain whether a block is protected or unprotected. Verification is performed either by inputting the Verify Block Protect command or by applying V_{ID} to the A9 pin, as for ID Read Mode, and setting the block address = $A0 = A6 = V_{IL}$ and $A1 = V_{IH}$. If the block is protected, 01H is output. If the block is unprotected, 00H is output.

Boot Block Protection

Boot block protection temporarily protects certain boot blocks using a method different from ordinary block protection. Neither V_{ID} nor a command sequence is required. Protection is performed simply by inputting V_{IL} on \overline{WP}/ACC . The target blocks are the two pairs of boot blocks. The top boot blocks are BA261 and BA262; the bottom boot blocks are BA0 and BA1. Inputting V_{IH} on \overline{WP}/ACC releases the mode. From now on, if it is necessary to protect these blocks, the ordinary Block Protection Mode must be used.



Hidden ROM Area

The TC58FVM7T2A/B2A features a 64-Kbyte hidden ROM area which is separate from the memory cells. The area consists of one block. Data Read, Write and Protect can be performed on this block. Because Protect cannot be released, once the block is protected, data in the block cannot be overwritten.

The hidden ROM area is located in the address space indicated in the HIDDEN ROM AREA ADDRESS TABLE. To access the Hidden ROM area, input a Hidden ROM Mode Entry command. The device now enters Hidden ROM Mode, allowing Read, Write, Erase and Block Protect to be executed. Write and Erase operations are the same as auto operations except that the device is in Hidden ROM Mode. To protect the hidden ROM area, use the block protection function. The operation of Block Protect here is the same as a normal Block Protect except that VIH rather than VID is input to $\overline{\text{RESET}}$. Once the block has been protected, protection cannot be released, even using the temporary block unprotection function. Use Block Protect carefully. Note that in Hidden ROM Mode, simultaneous operation cannot be performed for BANK3 in top boot type and for BANK0 in bottom boot type.

To exit Hidden ROM Mode, use the Hidden ROM Mode Exit command. This will return the device to Read Mode.

HIDDEN ROM AREA ADDRESS TABLE

TYPE	BOOT BLOCK	BYTE MOD	E	WORD MODE		
ITFE	ARCHITECTURE	ADDRESS RANGE	SIZE	ADDRESS RANGE	SIZE	
TC58FVM7T2A	TOP BOOT BLOCK	FF0000H~FFFFFFH	64 Kbytes	7F8000H~7FFFFFH	32 Kwords	
TC58FVM7B2A	BOTTOM BOOT BLOCK	000000H~00FFFFH	64 Kbytes	000000H~007FFFH	32 Kwords	



COMMON FLASH MEMORY INTERFACE (CFI)

The TC58FVM7T2A/B2A conforms to the CFI specifications. To read information from the device, input the Query command followed by the address. In Word Mode DQ8 \sim DQ15 all output 0s. To exit this mode, input the Reset command.

CFI CODE TABLE

ADDRESS A6~A0	DATA DQ15~DQ0	DESCRIPTION
10h 11h 12h	0051h 0052h 0059h	ASCII string "QRY"
13h 14h	0002h 0000h	Primary OEM command set 2: AMD/FJ standard type
15h 16h	0040h 0000h	Address for primary extended table
17h 18h	0000h 0000h	Alternate OEM command set 0: none exists
19h 1Ah	0000h 0000h	Address for alternate OEM extended table
1Bh	0023h	V _{DD} (min) (Write/Erase) DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
1Ch	0036h	V _{DD} (max) (Write/Erase) DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
1Dh	0000h	V _{PP} (min) voltage
1Eh	0000h	V _{PP} (max) voltage
1Fh	0004h	Typical time-out per single byte/word write (2 ^N μs)
20h	0000h	Typical time-out for minimum size buffer write (2 ^N μs)
21h	000Ah	Typical time-out per individual block erase (2 ^N ms)
22h	0000h	Typical time-out for full chip erase (2 ^N ms)
23h	0005h	Maximum time-out for byte/word write (2 ^N times typical)
24h	0000h	Maximum time-out for buffer write (2 ^N times typical)
25h	0004h	Maximum time-out per individual block erase (2 ^N times typical)
26h	0000h	Maximum time-out for full chip erase (2 ^N times typical)
27h	0018h	Device Size (2 ^N byte)
28h 29h	0002h 0000h	Flash device interface description 2: ×8/×16
2Ah 2Bh	0004h 0000h	Maximum number of bytes in multi-byte write (2 ^N)

ADDRESS A6~A0	DATA DQ15~DQ0	DESCRIPTION
2Ch	0002h	Number of erase block regions within device
2Dh 2Eh 2Fh 30h	0007h 0000h 0020h 0000h	Erase Block Region 1 information Bits 0~15: y = block number Bits 16~31: z = block size (z × 256 bytes)
31h 32h 33h 34h	00FEh 0000h 0000h 0001h	Erase Block Region 2 information
40h 41h 42h	0050h 0052h 0049h	ASCII string "PRI"
43h	0031h	Major version number, ASCII
44h	0031h	Minor version number, ASCII
45h	0000h	Address-Sensitive Unlock 0: Required 1: Not required
46h	0002h	Erase Suspend 0: Not supported 1: For Read-only 2: For Read & Write
47h	0001h	Block Protect 0: Not supported X: Number of blocks per group
48h	0001h	Block Temporary Unprotect 0: Not supported 1: Supported
49h	0004h	Block Protect/Unprotect scheme
4Ah	0001h	Simultaneous operation 0: Not supported 1: Supported
4Bh	0000h	Burst Mode 0: Not supported
4Ch	0001h	Page Mode 0: Not supported
4Dh	0085h	V _{ACC} (min) voltage DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
4Eh	0095h	V _{ACC} (max) voltage DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
4Fh	000Xh	Top/Bottom Boot Block Flag 2: TC58FVM7B2A 3: TC58FVM7T2A
50h	0001h	Program Suspend 0: Not supported 1: Supported

ADDRESS A6~A0	DATA DQ15~DQ0	DESCRIPTION
57h	0004h	Bank Organization 00h: Data at 4Ah is zero X: Number of Banks
58h	00XXh	Bank0 Region information X = Number of blocs Bank0 TOP: 20h BOTTOM: 27h
59h	00XXh	Bank1 Region information X = Number of blocks in Bank1 TOP: 60h BOTTOM: 60h
5Ah	00XXh	Bank2 Region information X = Number of blocks in Bank2 TOP: 60h BOTTOM: 60h
5Bh	00XXh	Bank3 Region information X = Number of blocks in Bank3 TOP: 27h BOTTOM: 20h



HARDWARE SEQUENCE FLAGS

The TC58FVM7T2A/B2A has a Hardware Sequence flag which allows the device status to be determined during an auto mode operation. The output data is read out using the same timing as that used when $\overline{CE} = \overline{OE} = V_{IL}$ in Read Mode. The RY/ \overline{BY} output can be either High or Low.

The device re-enters Read Mode automatically after an auto mode operation has been completed successfully. The Hardware Sequence flag is read to determine the device status and the result of the operation is verified by comparing the read-out data with the original data.

STATUS			DQ7	DQ6	DQ5	DQ3	DQ2	RY/BY	
	Auto Programming/Auto Page Programming			DQ7 (4)	Toggle	0	0	1	0
	Read in Pi	rogram Suspend ⁽¹⁾)	Data	Data	Data	Data	Data	High-Z
		Erase Hold Time	Selected ⁽²⁾	0	Toggle	0	0	Toggle	0
	In Auto	Erase Hold Time	Not-selected ⁽³⁾	0	Toggle	0	0	1	0
In Progress	Erase	Erase Auto Erase	Selected	0	Toggle	0	1	Toggle	0
In Progress			Not-selected	0	Toggle	0	1	1	0
		Read n Erase	Selected	1	1	0	0	Toggle	High-Z
	In Erase		Not-selected	Data	Data	Data	Data	Data	High-Z
	Suspend	Drogramming	Selected	DQ7	Toggle	0	0	Toggle	0
		Programming	Not-selected	DQ7 (4)	Toggle	0	0	1	0
	Auto Prog	ramming/Auto Pag	e Programming	DQ7	Toggle	1	0	1	0
Time Limit Exceeded	Auto Erase			0	Toggle	1	1	NA	0
	Programm	ning in Erase Suspe	Programming in Erase Suspend			1	0	NA	0

Notes:DQ outputs cell data and RY/BY goes High-Impedence when the operation has been completed.

DQ0 and DQ1 pins are reserved for future use.

- 0 is output on DQ0, DQ1 and DQ4.
- (1) Data output from an address to which Write is being performed is undefined.
- (2) Output when the block address selected for Auto Block Erase is specified and data is read from there. During Auto Chip Erase, all blocks are selected.
- (3) Output when a block address not selected for Auto Block Erase of same bank as selected block is specified and data is read from there.
- (4) In case of Page program operation is program data of (A0, A1, A2) = (1, 1, 1) in eleventh bus write cycle in word mode. Program data of (A-1, A0, A1, A2) = (1,1,1,1) in nineteenth bus write cycle in byte mode.

DQ7 (DATA polling)

During an Auto-Program or auto-erase operation, the device status can be determined using the data polling function. \overline{DATA} polling begins on the rising edge of \overline{WE} in the last bus cycle. In an Auto-Program operation, DQ7 outputs inverted data during the programming operation and outputs actual data after programming has finished. In an auto-erase operation, DQ7 outputs 0 during the Erase operation and outputs 1 when the Erase operation has finished. If an Auto-Program or auto-erase operation fails, DQ7 simply outputs the data.

When the operation has finished, the address latch is reset. Data polling is asynchronous with the OE signal.



DQ6 (Toggle bit 1)

The device status can be determined by the Toggle Bit function during an Auto-Program or auto-erase operation. The Toggle bit begins toggling on the rising edge of \overline{WE} in the last bus cycle. DQ6 alternately outputs a 0 or a 1 for each \overline{OE} access while \overline{CE} = VIL while the device is busy. When the internal operation has been completed, toggling stops and valid memory cell data can be read by subsequent reading. If the operation fails, the DQ6 output toggles.

If an attempt is made to execute an Auto Program operation on a protected block, DQ6 will toggle for around 3 μs . It will then stop toggling. If an attempt is made to execute an auto erase operation on a protected block, DQ6 will toggle for around 400 μs . It will then stop toggling. After toggling has stopped the device will return to Read Mode.

DQ5 (internal time-out)

If the internal timer times out during a Program or Erase operation, DQ5 outputs a 1. This indicates that the operation has not been completed within the allotted time.

Any attempt to program a 1 into a cell containing a 0 will fail (see Auto-Program Mode). In this case DQ5 outputs a 1. Either a hardware reset or a software Reset command is required to return the device to Read Mode.

DQ3 (Block Erase timer)

The Block Erase operation starts 50 μ s (the Erase Hold Time) after the rising edge of \overline{WE} in the last command cycle. DQ3 outputs a 0 for the duration of the Block Erase Hold Time and a 1 when the Block Erase operation starts. Additional Block Erase commands can only be accepted during the Block Erase Hold Time. Each Block Erase command input within the hold time resets the timer, allowing additional blocks to be marked for erasing. DQ3 outputs a 1 if the Program or Erase operation fails.

DQ2 (Toggle bit 2)

DQ2 is used to indicate which blocks have been selected for Auto Block Erase or to indicate whether the device is in Erase Suspend Mode.

If data is read continuously from the selected block during an Auto Block Erase, the DQ2 output will toggle. Now 1 will be output from non-selected blocks; thus, the selected block can be ascertained. If data is read continuously from the block selected for Auto Block Erase while the device is in Erase Suspend Mode, the DQ2 output will toggle. Because the DQ6 output is not toggling, it can be determined that the device is in Erase Suspend Mode. If data is read from the address to which data is being written during Erase Suspend in Programming Mode, DQ2 will output a 1.

RY/BY (READY/BUSY)

TC58FVM7T2A/B2A has a RY/\overline{BY} signal to indicate the device status to the host processor. A 0 (Busy state) indicates that an Auto-Program or auto-erase operation is in progress. A 1 (Ready state) indicates that the operation has finished and that the device can now accept a new command. RY/\overline{BY} outputs a 0 when an operation has failed.

RY/BY outputs a 0 after the rising edge of WE in the last command cycle.

During an Auto Block Erase operation, commands other than Erase Suspend are ignored. RY/\overline{BY} outputs a 1 during an Erase Suspend operation. The output buffer for the RY/\overline{BY} pin is an open-drain type circuit, allowing a wired-OR connection. A pull-up resistor must be inserted between VDD and the RY/\overline{BY} pin.



DATA PROTECTION

The TC58FVM7T2A/B2A includes a function which guards against malfunction or data corruption.

Protection against Program/Erase Caused by Low Supply Voltage

To prevent malfunction at power-on or power-down, the device will not accept commands while V_{DD} is below V_{LKO}. In this state, command input is ignored.

If VDD drops below VLKO during an Auto Operation, the device will terminate Auto-Program execution. In this case, Auto operation is not executed again when VDD return to recommended VDD voltage Therefore, command need to be input to execute Auto operation again.

When VDD > VLKO, make up countermeasure to be input accurately command in system side please.

Protection against Malfunction Caused by Glitches

To prevent malfunction during operation caused by noise from the system, the device will not accept pulses shorter than 3 ns (Typ.) input on \overline{WE} , \overline{CE} or \overline{OE} . However, if a glitch exceeding 3 ns (Typ.) occurs and the glitch is input to the device malfunction may occur.

The device uses standard JEDEC commands. It is conceivable that, in extreme cases, system noise may be misinterpreted as part of a command sequence input and that the device will acknowledge it. Then, even if a proper command is input, the device may not operate. To avoid this possibility, clear the Command Register before command input. In an environment prone to system noise, Toshiba recommend input of a software or hardware reset before command input.

Protection against Malfunction at Power-on

To prevent damage to data caused by sudden noise at power-on, when power is turned on with $WE = CE = V_{IL}$ the device does not latch the command on the first rising edge of \overline{WE} or \overline{CE} . Instead, the device automatically Resets the Command Register and enters Read Mode.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RANGE	UNIT
V_{DD}	V _{DD} Supply Voltage	-0.6~4.6	V
V _{IN}	Input Voltage	-0.6~V _{DD} + 0.5 (≤ 4.6) ⁽¹⁾	٧
V_{DQ}	Input/Output Voltage	-0.6~V _{DD} + 0.5 (≤ 4.6) ⁽¹⁾	٧
V _{IDH}	Maximum Input Voltage for A9, $\overline{\text{OE}}$ and $\overline{\text{RESET}}^{(2)}$	13.0	٧
V _{ACCH}	Maximum Input Voltage for WP/ACC (2)	10.5	٧
P_{D}	Power Dissipation	600	mW
T _{solder}	Soldering Temperature (10s)	260	°C
T _{stg}	Storage Temperature	−55~150	°C
T _{opr}	Operating Temperature	−40~85	°C
Ioshort	Output Short-Circuit Current ⁽³⁾	100	mA

- (1) This level may undershoot to -2.0 V for periods < 20 ns, and may overshoot to +2.0 V for periods < 20 ns.
- (2) Do not apply VID/VACC when the supply voltage is not within the device's recommended operating voltage range.
- (3) Outputs should be shorted for no more than one second. No more than one output should be shorted at a time.

CAPACITANCE (Ta = 25°C, f = 1 MHz)

SYMBOL	PARAMETER	CONDITION	MAX	UNIT
C _{IN}	Input Pin Capacitance	$V_{IN} = 0 V$	5	pF
C _{OUT}	Output Pin Capacitance	V _{OUT} = 0 V	8	pF
C _{IN2}	Control Pin Capacitance	$V_{IN} = 0 V$	7	pF

This parameter is periodically sampled and is not tested for every device.

RECOMMENDED DC OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN	MAX	UNIT
V_{DD}	V _{DD} Supply Voltage	2.3	3.6	
V _{IH}	Input High-Level Voltage	$0.7 \times V_{DD}$	V _{DD} + 0.3	
V_{IL}	Input Low-Level Voltage	-0.3	$0.2 \times V_{DD}$	V
V_{ID}	High-Level Voltage for A9, $\overline{\text{OE}}$ and $\overline{\text{RESET}}$	11.4	12.6	
V _{ACC}	High-Level Voltage for WP/ACC	8.5	9.5	
Та	Operating Temperature	-40	85	°C



DC CHARACTERISTICS

SYMBOL	PARAMETER	CONDITION	MIN	TYP	MAX	UNIT
I _{LI}	Input Leakage Current	$0\ V \leq V_{IN} \leq V_{DD}$	_		±1	^
I _{LO}	Output Leakage Current	$0 \text{ V} \leq V_{OUT} \leq V_{DD}$	_	_	±1	μА
V	Output High Voltage	$I_{OH} = -0.1 \text{ mA}$	V _{DD} – 0.4	_	_	
V _{OH}	Output High Voltage	I _{OH} = -2.5 mA	$0.85 \times V_{DD}$	_	_	V
V_{OL}	Output Low Voltage	I _{OL} = 4.0 mA	_	_	0.4	
I _{DDO1}	V _{DD} Average Random Read Current	$V_{IN} = V_{IH}/V_{IL}$, $I_{OUT} = 0$ mA $t_{RC} = 100$ ns (MIN)	_	35	55	
I _{DDO2}	V _{DD} Average Program Current	$V_{IN} = V_{IH}/V_{IL}, I_{OUT} = 0 \text{ mA}$	_	8	15	
I _{DDO3}	V _{DD} Average Erase Current	$V_{IN} = V_{IH}/V_{IL}, I_{OUT} = 0 \text{ mA}$	_	8	15	
I _{DDO4}	V _{DD} Average Read-While-Program Current	$V_{IN} = V_{IH}/V_{IL}, I_{OUT} = 0 \text{ mA}$ $t_{RC} = 100 \text{ ns (MIN)}$	_	43	70	
I _{DDO5}	V _{DD} Average Read-while-Erase Current	$V_{IN} = V_{IH}/V_{IL}$, $I_{OUT} = 0$ mA $t_{RC} = 100$ ns (MIN)	_	43	70	mA
I _{DDO6}	V _{DD} Average Program-while- Erase-Suspend Current	V _{IN} = V _{IH} /V _{IL} , I _{OUT} = 0 mA	_	8	15	
I _{DDO7}	V _{DD} Average Page Read Current	$V_{IN} = V_{IH}/V_{IL}$, $I_{OUT} = 0$ mA $t_{PRC} = 25$ ns (MIN)	_	1	5	
I _{DDO8}	V _{DD} Average Address Increment Read Current ⁽²⁾	$\begin{split} &V_{IN}=V_{IH}/V_{IL},\ I_{OUT}=0\ mA\\ &t_{RC}=100\ ns\ (MIN)\\ &t_{PRC}=25\ ns\ (MIN) \end{split}$	_	5	11	
I _{DDS1}	V _{DD} Standby Current	$\overline{CE} = \overline{RESET} = V_{DD}$ or $\overline{RESET} = V_{SS}$	_	2	10	
I _{DDS2}	V _{DD} Standby Current (Automatic Sleep Mode ⁽¹⁾)	$V_{IH} = V_{DD}$ $V_{IL} = V_{SS}$	_	2	10	μΑ
I _{ID}	High-Voltage Input Current for A9, OE and RESET	11.4 V ≤ V _{ID} ≤ 12.6 V	_	_	35	
I _{ACC}	High-Voltage Input Current for WP/ACC	8.5 V ≤ V _{ACC} ≤ 9.5 V	_	_	20	mA
V _{LKO}	Low-V _{DD} Lock-out Voltage	_	1.5	_	2.0	V

⁽¹⁾ The device enters Automatic Sleep Mode in which the address remains fixed for during 150 ns.

AC TEST CONDITIONS

PARAMETER	CONDITION
Input Pulse Level	V _{DD} , 0.0 V
Input Pulse Rise and Fall Time (10%~90%)	5 ns
Timing Measurement Reference Level (input)	VDD/2, VDD/2
Timing Measurement Reference Level (output)	VDD/2, VDD/2
Output Load	C _L (100 pF) + 1 TTL Gate/C _L (30 pF) + 1 TTL Gate

⁽²⁾ $(I_{DDO1} + I_{DDO7} \times 7)$ 8words



AC CHARACTERISTICS AND OPERATING CONDITIONS

	Product name	TC58FVM7T2AFT65/TC58FVM7B2AFT65								
	VDD voltage (V)		VDD = 2	2.7-3.6\	/	VDD = 2.3-3.6V				
	Output load capacitance (CL)	30	pF	100) pF	30 pF		F 100 pl		Unit
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	
t _{RC}	Read Cycle Time	65	_	70	_	70	_	75	_	ns
t _{PRC}	Page Read Cycle Time	25	_	30	_	30	_	35	_	ns
t _{ACC}	Address Access Time	_	65	_	70	_	70	_	75	ns
t _{CE}	CE Access Time	_	65	_	70	_	70	_	75	ns
t _{OE}	OE Access Time	_	25	_	30		30	_	35	ns
t _{PACC}	Page Access Time	_	25	_	30	_	30	_	35	ns
t _{CEE}	CE to Output Low-Z	0	_	0	_	0	_	0	_	ns
t _{OEE}	OE to Output Low-Z	0		0		0	_	0		ns
t _{OH}	Output Data Hold Time	0		0		0		0		ns
t _{DF1}	CE to Output High-Z	_	25	_	25	_	25	_	25	ns
t _{DF2}	OE to Output High-Z		25		25	_	25	_	25	ns

	Product name		TC58FVM7T2AFT80/TC58FVM7B2AFT80							
	VDD voltage (V)		VDD = 2	2.7-3.6\	/	VDD = 2.3-3.6 V				
	Output load capacitance (CL)	30	pF	100) pF	30 pF		F 100 pF		Unit
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	
t _{RC}	Read Cycle Time	80		85	_	85	_	90		ns
t _{PRC}	Page Read Cycle Time	30	_	35	_	35	_	40		ns
t _{ACC}	Address Access Time		80		85	_	85		90	ns
t _{CE}	CE Access Time	_	80	_	85	_	85		90	ns
t _{OE}	OE Access Time	_	30	_	35	_	35	_	40	ns
t _{PACC}	Page Access Time	_	30	_	35	_	35	_	40	ns
t _{CEE}	CE to Output Low-Z	0	_	0	_	0	_	0	_	ns
toee	OE to Output Low-Z	0	_	0	_	0		0	_	ns
t _{OH}	Output Data Hold Time	0		0		0		0		ns
t _{DF1}	CE to Output High-Z		25		25		25	_	25	ns
t _{DF2}	OE to Output High-Z	_	25	_	25	_	25	_	25	ns



BLOCK PROTECT

SYMBOL	PARAMETER	MIN	MAX	UNIT
t_{VPT}	V _{ID} Transition Time	4	_	μS
t _{VPS}	V _{ID} Set-up Time	4	_	μS
t _{CESP}	CE Set-up Time	4	_	μS
t _{VPH}	OE Hold Time	4	_	μS
t _{PPLH}	WE Low-Level Hold Time	100	_	μS

PROGRAM AND ERASE CHARACTERISTICS

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT
	Auto-Program Time (Byte Mode)	_	8	300	μs
t _{PPW}	Auto-Program Time (Word Mode)		11	300	μS
t _{PPAW}	Auto-Page program time	_	45	2400	μS
t _{PCEW}	Auto Chip Erase Time	_	184	2630	s
t _{PBEW}	Auto Block Erase Time		0.7	10	s
t _{EW}	Erase/Program Cycle	10 ⁵	_	_	Cycles

^{*} Auto Chip Erase Time and Auto Block Erase Time include internal pre program time.



COMMAND WRITE/PROGRAM/ERASE CYCLE

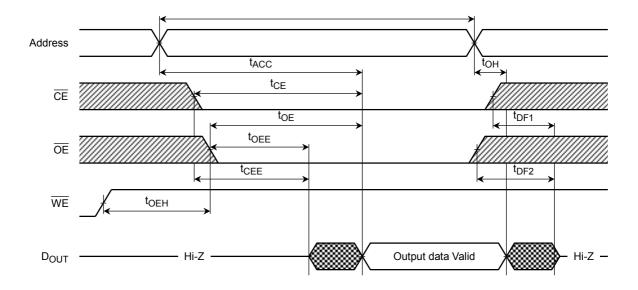
SYMBOL	PARAMETER			UNIT
		MIN	MAX	
t _{CMD}	Command Write Cycle Time	65	_	ns
tAS	Address Set-up Time/ BYTE Set-up Time	0	_	ns
t _{AH}	Address Hold Time/BYTE Hold Time	30		ns
t _{DS}	Data Set-up Time	30		ns
t _{DH}	Data Hold Time	0		ns
tWELH	WE Low-Level Hold Time (WE Control)	30	_	ns
tWEHH	WE High-Level Hold Time (WE Control)	20	_	ns
t _{CES}	CE Set-up Time to WE Active (WE Control)	0	_	ns
t _{CEH}	CE Hold Time from WE High Level (WE Control)	0	_	ns
t _{CELH}	CE Low-Level Hold Time (CE Control)	30	—	ns
t _{CEHH}	CE High-Level Hold Time (CE Control)	20		ns
t _{WES}	WE Set-up time to CE Active (CE Control)	0	—	ns
t _{WEH}	WE Hold Time from CE High Level (CE Control)	0		ns
toes	OE Set-up Time	0	_	ns
t _{OEHP}	OE Hold Time (Toggle, Data Polling)	10	_	ns
t _{OEHT}	OE High-Level Hold Time (Toggle)	20	_	ns
t _{AHT}	Address Hold Time (Toggle)	0	_	ns
t _{AST}	Address Set-up Time (Toggle)	0	_	ns
t _{BEH}	Erase Hold Time	50	_	μS
t _{VDS}	V _{DD} Set-up Time	500	_	μS
	Program/Erase Valid to RY/BY Delay	_	90	ns
t _{BUSY}	Program/Erase Valid to RY/BY Delay during Suspend Mode	_	300	ns
t _{RP}	RESET Low-Level Hold Time	500	_	ns
t _{READY}	RESET Low-Level to Read Mode	_	20	μS
t _{RB}	RY/BY Recovery Time	0	_	ns
t _{RH}	RESET Recovery Time	50	_	ns
t _{CEBTS}	CE Set-up time BYTE Transition	5	_	ns
t _{BTD}	BYTE to Output High-Z	_	30	ns
tsusp	Program Suspend Command to Suspend Mode	_	1.6	μS
tsuspa	Page Program Suspend Command to Suspend Mode	_	2.0	μS
t _{RESP}	Program Resume Command to Program Mode	_	1	μS
tsuse	Erase Suspend Command to Suspend Mode	_	15	μS
t _{RESE}	Erase Resume Command to Erase Mode	_	1	μS



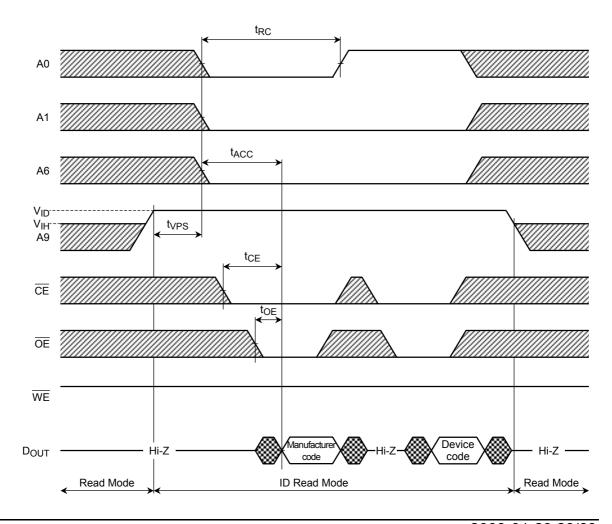
TIMING DIAGRAMS



Read/ID Read Operation

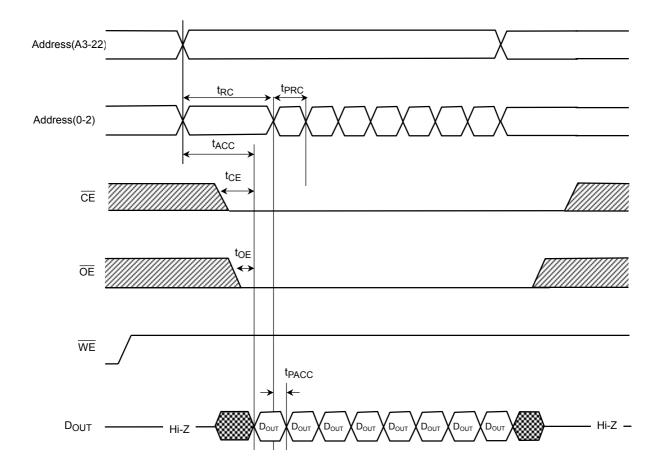


ID Read Operation (apply V_{ID} to A9)

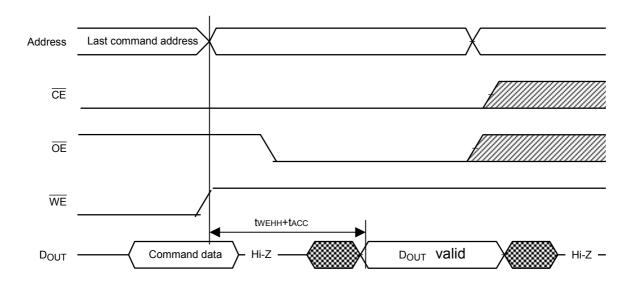




Page Read Operation



Read after command input (Only Hidden Rom/CFI Read)

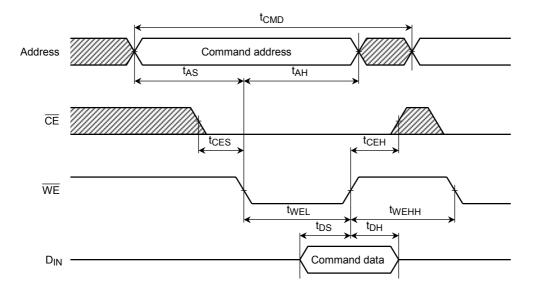




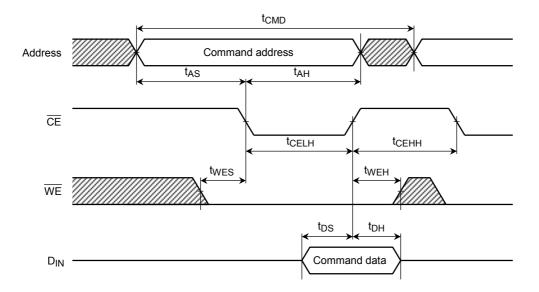
Command Write Operation

This is the timing of the Command Write Operation. The timing which is described in the following pages is essentially the same as the timing shown on this page.

• WE Control

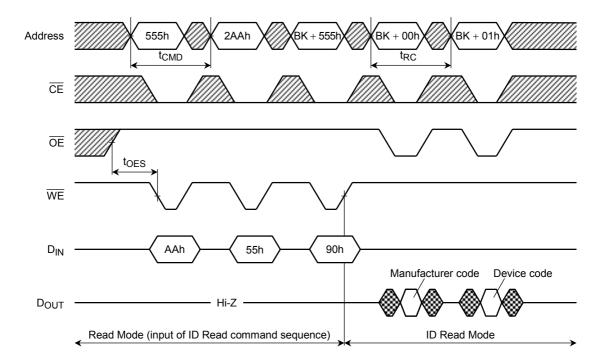


$\bullet \quad \overline{\rm CE} \ {\rm Control}$

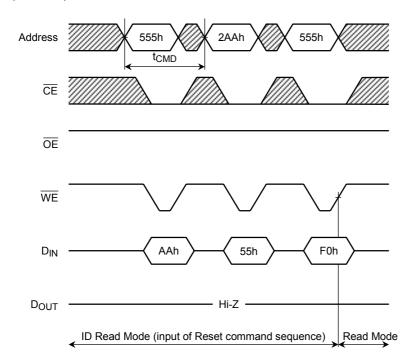




ID Read Operation (input command sequence)



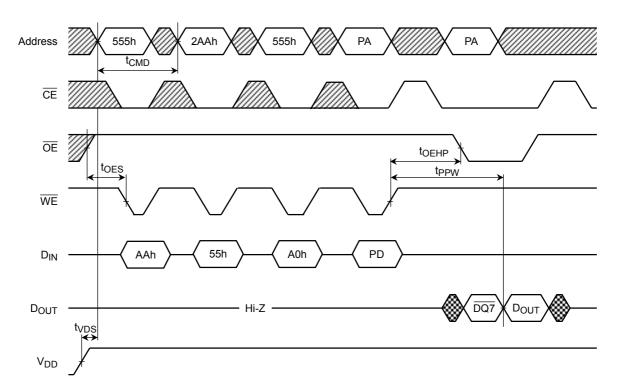
(Continued)



Note: Word Mode address shown. BK: Bank address



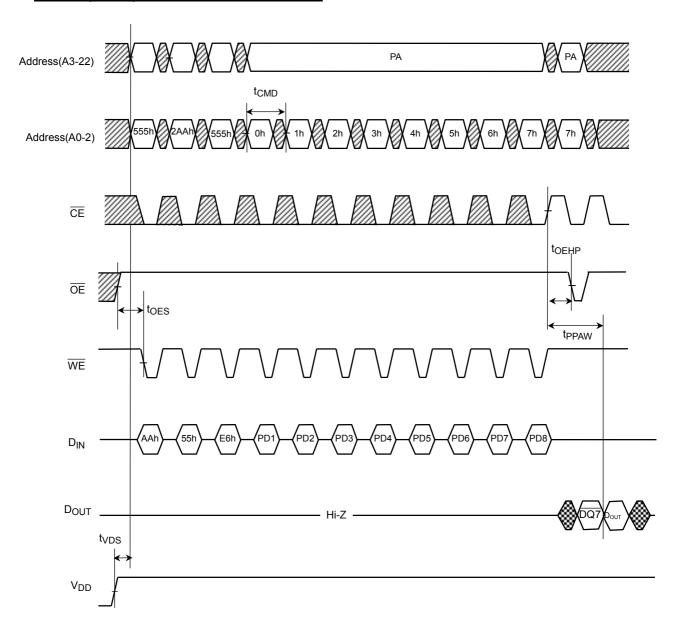
Auto-Program Operation (WE Control)



Note: Word Mode address shown. PA: Program address PD: Program data



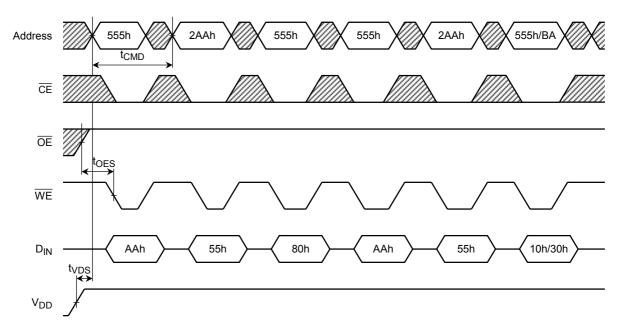
Auto Page Program Operation (WE Control)



Note: Word Mode address shown.
PA: Program address
PD: Program Data



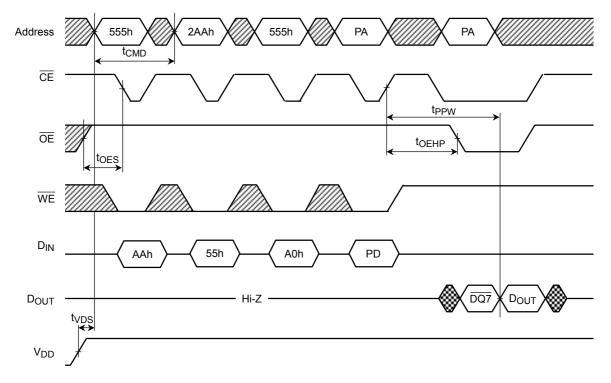
Auto Chip Erase/Auto Block Erase Operation (WE Control)



Note: Word Mode address shown.

BA: Block address for Auto Block Erase operation

Auto-Program Operation (CE Control)



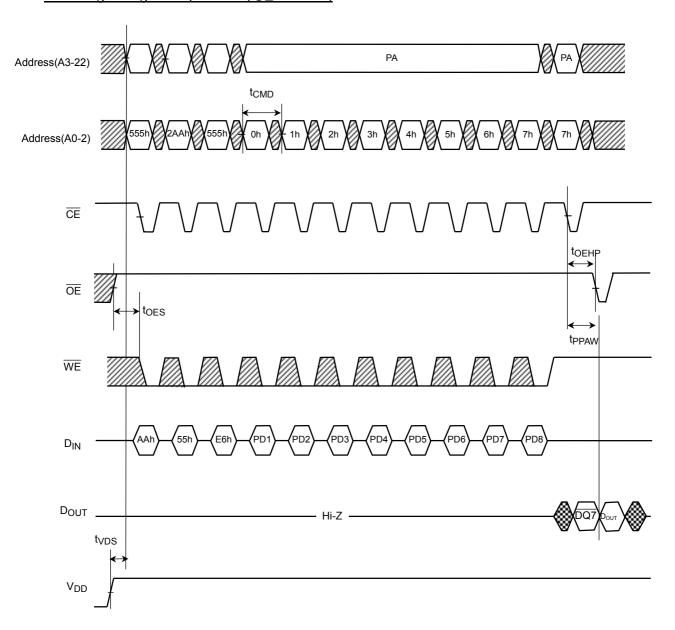
Note: Word Mode address shown.

PA: Program address

PD: Program data



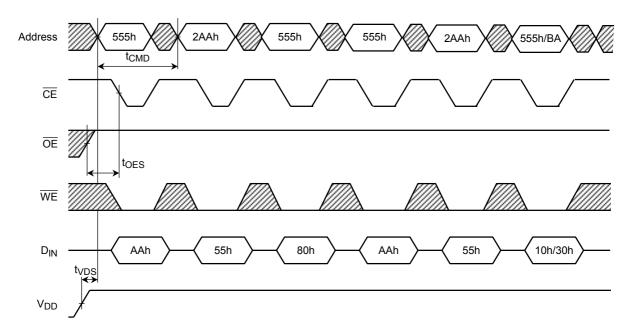
Auto Page Program Operation (CE Control)



Note: Word Mode address shown.
PA: Program address
PD: Program data



Auto Chip Erase/Auto Block Erase Operation (CE Control)

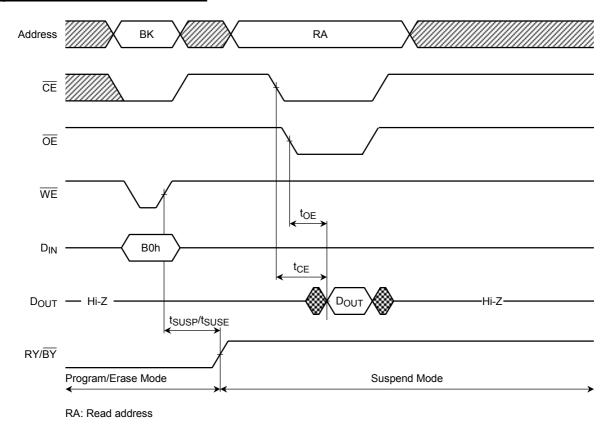


Note: Word Mode address shown.

BA: Block address for Auto Block Erase operation

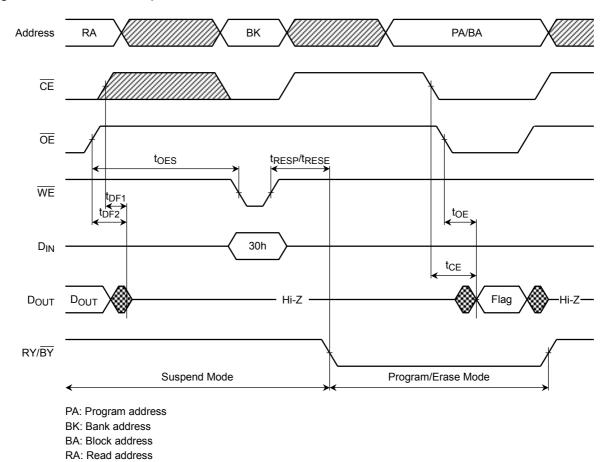


Program/Erase Suspend Operation



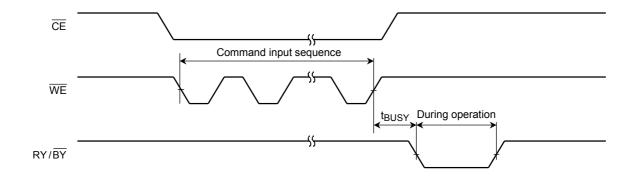
Program/Erase Resume Operation

Flag: Hardware Sequence flag

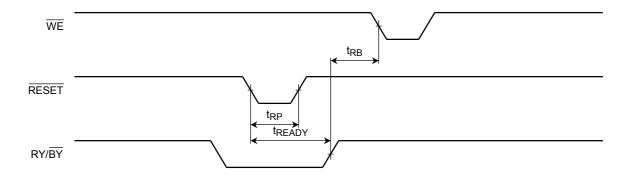




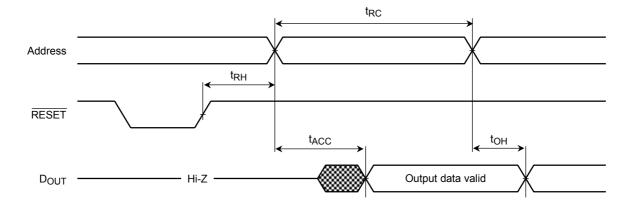
RY/BY during Auto Program/Erase Operation



Hardware Reset Operation

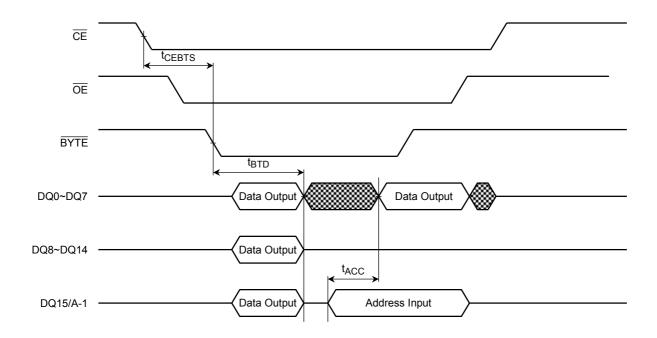


Read after RESET

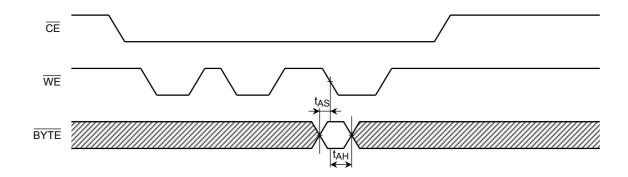




BYTE during Read Operation

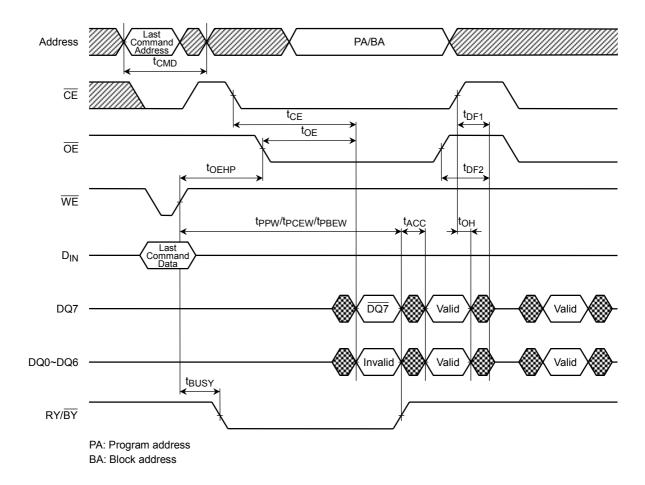


BYTE during Write Operation

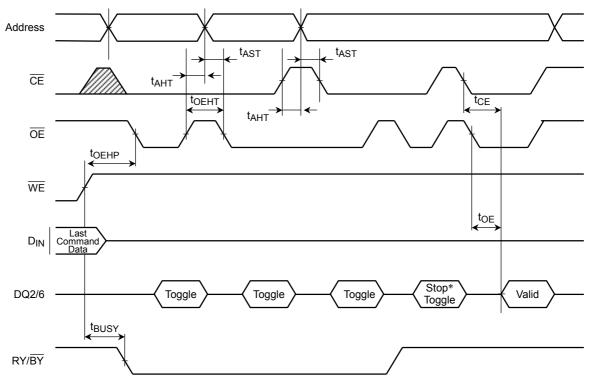




Hardware Sequence Flag (DATA Polling)

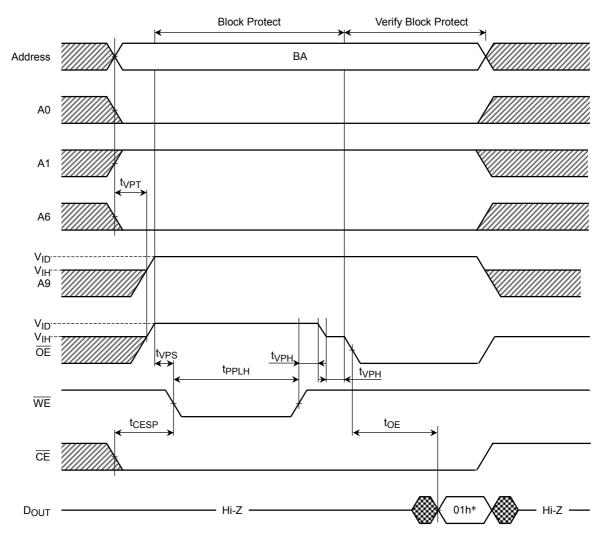


Hardware Sequence Flag (Toggle bit)





Block Protect 1 Operation

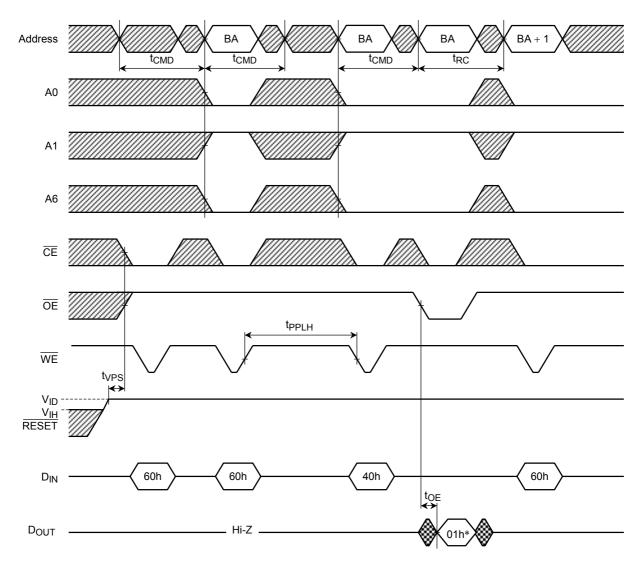


BA: Block address

*: 01h indicates that block is protected.



Block Protect 2 Operation



BA: Block address

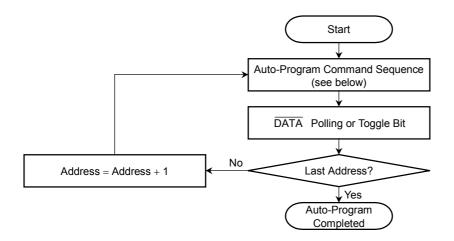
BA + 1: Address of next block

*: 01h indicates that block is protected.

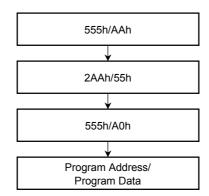


FLOWCHARTS

Auto-Program



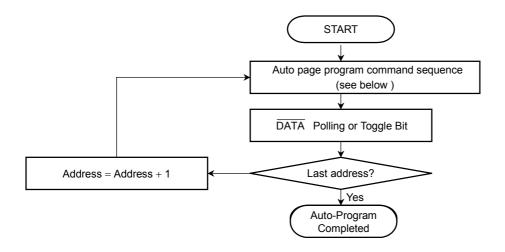
Auto-Program Command Sequence (address/data)

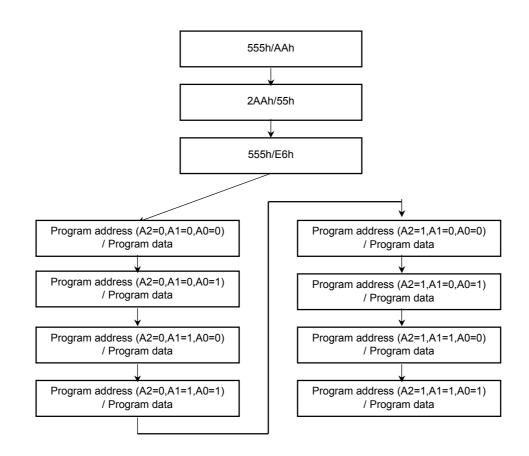


Note: The above command sequence takes place in Word Mode.



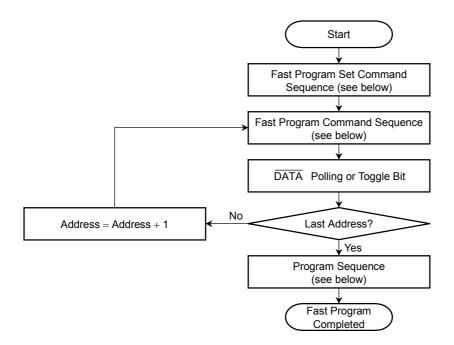
Auto-Page Program

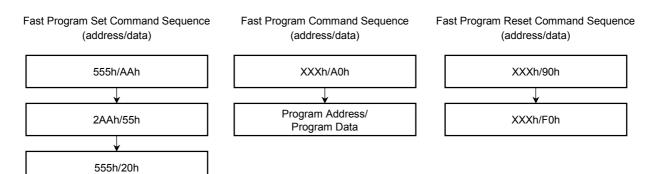






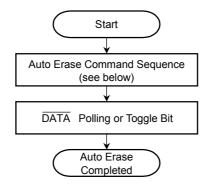
Fast Program

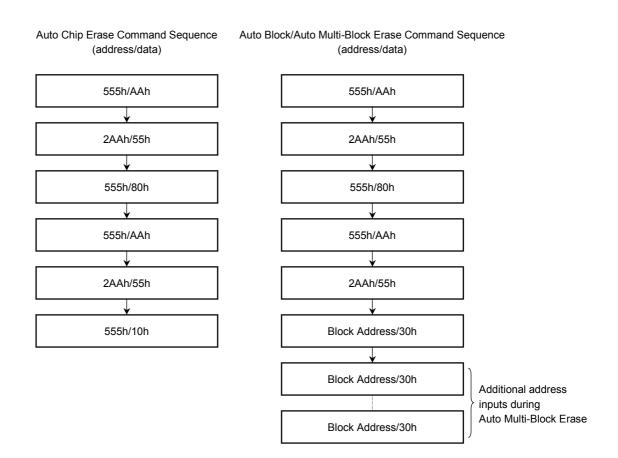






Auto Erase

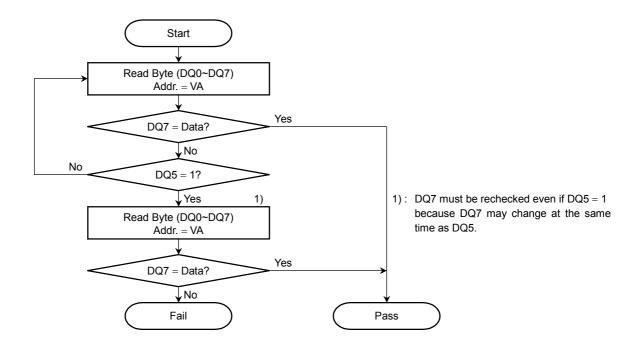




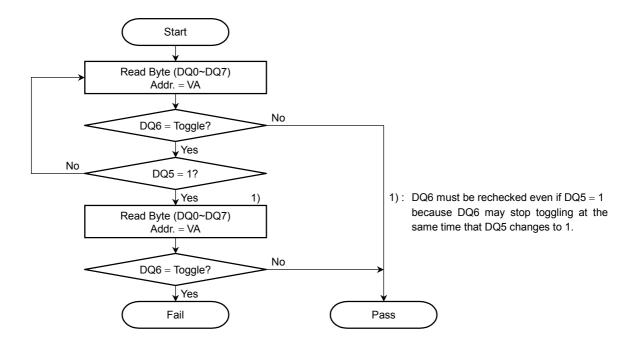
Note: The above command sequence takes place in Word Mode.



DQ7 DATA Polling



DQ6 Toggle Bit



VA: Byte address for programming

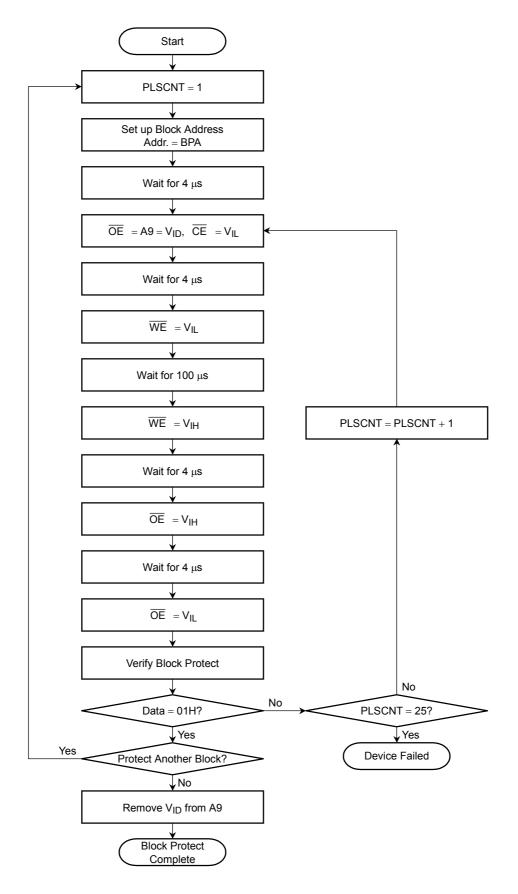
Any of the addresses within the block being erased during a Block Erase operation

"Don't care" during a Chip Erase operation

Any address not within the current block during an Erase Suspend operation



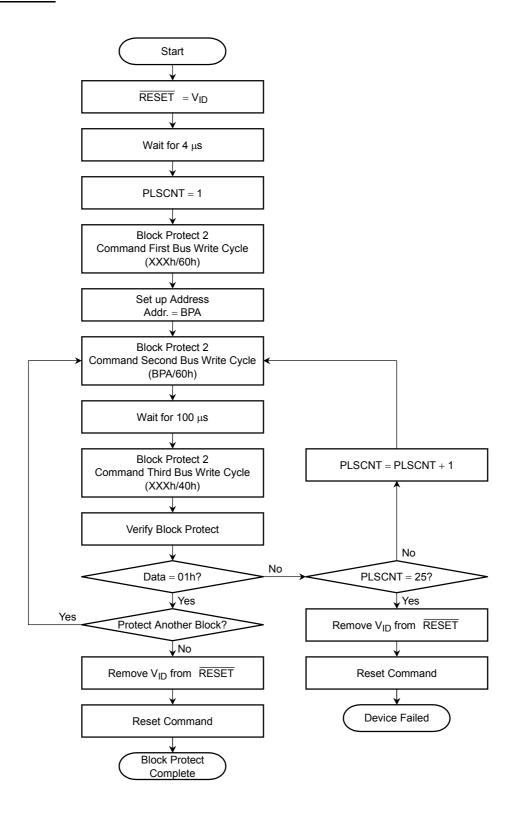
Block Protect 1



BPA: Block Address and ID Read Address (A6, A1, A0) ID Read Address = (0, 1, 0)



Block Protect 2



BPA: Block Address and ID Read Address (A6, A1, A0) ID Read Address = (0, 1, 0)



BLOCK ADDRESS TABLES

(1) TC58FVM7T2A (top boot block)

	<u> </u>						DDRE	SS						
BANK	BLOCK		BANK										ADDRES	S RANGE
#	#	AL A22	DDRES A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA0	L	L	L	L	L	L	L	L	*	*	*	000000h~00FFFFh	000000h~007FFFh
	BA1	L	L	L	L	L	L	L	Н	*	*	*	010000h~01FFFFh	008000h~00FFFFh
	BA2	L	L	L	L	L	L	Н	L	*	*	*	020000h~02FFFFh	010000h~017FFFh
	BA3	L	L	L	L	L	L	Н	Н	*	*	*	030000h~03FFFFh	018000h~01FFFFh
	BA4	L	L	L	L	L	Н	L	L	*	*	*	040000h~04FFFFh	020000h~027FFFh
	BA5	L	L	L	L	L	Н	L	Н	*	*	*	050000h~05FFFFh	028000h~02FFFFh
	BA6	L	L	L	L	L	Н	Н	L	*	*	*	060000h~06FFFFh	030000h~037FFFh
	BA7	L	L	L	L	L	Н	Н	Н	*	*	*	070000h~07FFFh	038000h~03FFFFh
	BA8	L	L	L	L	Н	L	L	L	*	*	*	080000h~08FFFFh	040000h~047FFFh
	BA9	L	L	L	L	Н	L	L	Н	*	*	*	090000h~09FFFh	048000h~04FFFFh
	BA10	L	L	L	L	Н	L	Н	L	*	*	*	0A0000h~0AFFFFh	050000h~057FFFh
	BA11	L	L	L	L	Н	L	Н	Н	*	*	*	0B0000h~0BFFFFh	058000h~05FFFFh
	BA12	L	L	L	L	Н	Н	L	L	*	*	*	0C0000h~0CFFFh	060000h~067FFFh
	BA13	L	L	L	L	Н	Н	L	Н	*	*	*	0D0000h~0DFFFFh	068000h~06FFFFh
	BA14	L	L	L	L	Н	Н	Н	L	*	*	*	0E0000h~0EFFFh	070000h~077FFFh
BK0	BA15	L	L	L	L	Н	Н	Н	Н	*	*	*	0F0000h~0FFFFh	078000h~07FFFh
BRU	BA16	L	L	L	Н	L	L	L	L	*	*	*	100000h~10FFFFh	080000h~087FFFh
	BA17	L	L	L	Н	L	L	L	Н	*	*	*	110000h~11FFFFh	088000h~08FFFFh
	BA18	L	L	L	Н	L	L	Н	L	*	*	*	120000h~12FFFFh	090000h~097FFh
	BA19	L	L	L	Н	L	L	Н	Н	*	*	*	130000h~13FFFFh	098000h~09FFFFh
	BA20	L	L	L	Н	L	Н	L	L	*	*	*	140000h~14FFFFh	0A0000h~0A7FFFh
	BA21	L	L	L	Н	L	Н	L	Н	*	*	*	150000h~15FFFFh	0A8000h~0AFFFh
	BA22	L	L	L	Н	L	Н	Н	L	*	*	*	160000h~16FFFFh	0B0000h~0B7FFh
	BA23	L	L	L	Н	L	Н	Н	Н	*	*	*	170000h~17FFFFh	0B8000h~0BFFFFh
	BA24	L	L	L	Н	Н	L	L	L	*	*	*	180000h~18FFFFh	0C0000h~0C7FFh
	BA25	L	L	L	Н	Н	L	L	Н	*	*	*	190000h~19FFFFh	0C8000h~0CFFFh
	BA26	L	L	L	Н	Н	L	Н	L	*	*	*	1A0000h~1AFFFFh	0D0000h~0D7FFFh
	BA27	L	L	L	Н	Н	L	Н	Н	*	*	*	1B0000h~1BFFFFh	0D8000h~0DFFFFh
	BA28	L	L	L	Н	Н	Н	L	L	*	*	*	1C0000h~1CFFFFh	0E0000h~0E7FFh
	BA29	L	L	L	Н	Н	Н	L	Н	*	*	*	1D0000h~1DFFFFh	0E8000h~0EFFFh
	BA30	L	L	L	Н	Н	Н	Н	L	*	*	*	1E0000h~1EFFFFh	0F0000h~0F7FFh
	BA31	L	L	L	Н	Н	Н	Н	Н	*	*	*	1F0000h~1FFFFh	0F8000h~0FFFFh

					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DDRE										ADDRES	S RANGE
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA32	L	L	Н	L	L	L	L	L	*	*	*	200000h~20FFFh	100000h~107FFFh
	BA33	L	L	Н	L	L	L	L	Н	*	*	*	210000h~21FFFFh	108000h~10FFFFh
	BA34	L	L	Н	L	L	L	Н	L	*	*	*	220000h~22FFFFh	110000h~117FFFh
	BA35	L	L	Н	L	L	L	Н	Н	*	*	*	230000h~23FFFFh	118000h~11FFFFh
	BA36	L	L	Н	L	L	Н	L	L	*	*	*	240000h~24FFFFh	120000h~127FFFh
	BA37	L	L	Н	L	L	Н	L	Н	*	*	*	250000h~25FFFFh	128000h~12FFFFh
	BA38	L	L	Н	L	L	Н	Н	L	*	*	*	260000h~26FFFh	130000h~137FFFh
	BA39	L	L	Н	L	L	Н	Н	Н	*	*	*	270000h~27FFFFh	138000h~13FFFFh
	BA40	L	L	Н	L	Н	L	L	L	*	*	*	280000h~28FFFFh	140000h~147FFFh
	BA41	L	L	Н	L	Н	L	L	Н	*	*	*	290000h~29FFFh	148000h~14FFFFh
	BA42	L	L	Н	L	Н	L	Н	L	*	*	*	2A0000h~2AFFFh	150000h~157FFFh
	BA43	L	L	Н	L	Н	L	Н	Н	*	*	*	2B0000h~2BFFFFh	158000h~15FFFFh
	BA44	L	L	Н	L	Н	Н	L	L	*	*	*	2C0000h~2CFFFh	160000h~167FFFh
	BA45	L	L	Н	L	Н	Н	L	Н	*	*	*	2D0000h~2DFFFFh	168000h~16FFFFh
	BA46	L	L	Н	L	Н	Н	Н	L	*	*	*	2E0000h~2EFFFh	170000h~177FFFh
BK1	BA47	L	L	Н	L	Н	Н	Н	Н	*	*	*	2F0000h~2FFFFh	178000h~17FFFFh
BKI	BA48	L	L	Н	Н	L	L	L	L	*	*	*	300000h~30FFFFh	180000h~187FFFh
	BA49	L	L	Н	Н	L	L	L	Н	*	*	*	310000h~31FFFFh	188000h~18FFFFh
	BA50	L	L	Η	Η	L	L	Н	L	*	*	*	320000h~32FFFFh	190000h~197FFFh
	BA51	L	L	Ι	Ι	Ы	Ы	Ι	Ι	*	*	*	330000h~33FFFFh	198000h~19FFFFh
	BA52	L	L	Н	Н	L	Н	L	L	*	*	*	340000h~34FFFFh	1A0000h~1A7FFFh
	BA53	L	L	Ι	Ι	Ы	Ι	L	Ι	*	*	*	350000h~35FFFFh	1A8000h~1AFFFFh
	BA54	L	L	Н	Н	L	Н	Н	L	*	*	*	360000h~36FFFFh	1B0000h~1B7FFFh
	BA55	L	L	Η	Η	L	Η	Н	Η	*	*	*	370000h~37FFFFh	1B8000h~1BFFFFh
	BA56	L	L	Ι	Ι	Ι	Ы	Ы	Ы	*	*	*	380000h~38FFFFh	1C0000h~1C7FFFh
	BA57	L	L	Н	Н	Н	L	L	Н	*	*	*	390000h~39FFFFh	1C8000h~1CFFFFh
	BA58	L	L	Н	Н	Н	L	Н	L	*	*	*	3A0000h~3AFFFFh	1D0000h~1D7FFFh
	BA59	L	L	Н	Н	Н	L	Н	Н	*	*	*	3B0000h~3BFFFFh	1D8000h~1DFFFFh
	BA60	L	L	Н	Н	Н	Н	L	L	*	*	*	3C0000h~3CFFFh	1E0000h~1E7FFFh
	BA61	L	L	Н	Н	Н	Н	L	Н	*	*	*	3D0000h~3DFFFFh	1E8000h~1EFFFFh
	BA62	L	L	Н	Н	Н	Н	Н	L	*	*	*	3E0000h~3EFFFh	1F0000h~1F7FFFh
	BA63	L	L	Н	Н	Н	Н	Н	Н	*	*	*	3F0000h~3FFFFh	1F8000h~1FFFFFh

					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DDRE										ADDRES	S RANGE
"		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA64	L	Н	L	L	L	L	L	L	*	*	*	400000h~40FFFh	200000h~207FFFh
	BA65	L	Н	L	L	L	L	L	Н	*	*	*	410000h~41FFFFh	208000h~20FFFFh
	BA66	L	Н	L	L	L	L	Н	L	*	*	*	420000h~42FFFFh	210000h~217FFFh
	BA67	L	Н	L	L	L	L	Н	Н	*	*	*	430000h~43FFFFh	218000h~21FFFFh
	BA68	L	Н	L	L	L	Н	L	L	*	*	*	440000h~44FFFFh	220000h~227FFFh
	BA69	L	Н	L	L	L	Н	L	Н	*	*	*	450000h~45FFFFh	228000h~22FFFFh
	BA70	L	Н	L	L	L	Н	Н	L	*	*	*	460000h~46FFFh	230000h~237FFFh
	BA71	L	Н	L	L	L	Н	Н	Н	*	*	*	470000h~47FFFFh	238000h~23FFFFh
	BA72	L	Н	L	L	Н	L	L	L	*	*	*	480000h~48FFFFh	240000h~247FFFh
	BA73	L	Н	L	L	Н	L	L	Н	*	*	*	490000h~49FFFh	248000h~24FFFFh
	BA74	L	Н	L	L	Н	L	Н	L	*	*	*	4A0000h~4AFFFFh	250000h~257FFFh
	BA75	L	Н	L	L	Н	L	Н	Н	*	*	*	4B0000h~4BFFFFh	258000h~25FFFFh
	BA76	L	Н	L	L	Н	Н	L	L	*	*	*	4C0000h~4CFFFh	260000h~267FFFh
	BA77	L	Н	L	L	Н	Н	L	Н	*	*	*	4D0000h~4DFFFFh	268000h~26FFFFh
	BA78	L	Н	L	L	Н	Н	Н	L	*	*	*	4E0000h~4EFFFh	270000h~277FFFh
BK1	BA79	L	Н	L	L	Н	Н	Н	Н	*	*	*	4F0000h~4FFFFh	278000h~27FFFFh
BKI	BA80	L	Н	L	Н	L	L	L	L	*	*	*	500000h~50FFFh	280000h~287FFFh
	BA81	L	Н	L	Н	L	L	L	Н	*	*	*	510000h~51FFFFh	288000h~28FFFFh
	BA82	L	Н	L	Н	L	L	Н	L	*	*	*	520000h~52FFFFh	290000h~297FFFh
	BA83	L	Н	L	Н	L	L	Н	Н	*	*	*	530000h~53FFFFh	298000h~29FFFFh
	BA84	L	Н	L	Н	L	Н	L	L	*	*	*	540000h~54FFFFh	2A0000h~2A7FFFh
	BA85	L	Н	L	Н	L	Н	L	Н	*	*	*	550000h~55FFFFh	2A8000h~2AFFFFh
	BA86	L	Н	L	Н	L	Н	Н	L	*	*	*	560000h~56FFFh	2B0000h~2B7FFFh
	BA87	L	Н	L	Н	L	Н	Н	Н	*	*	*	570000h~57FFFh	2B8000h~2BFFFFh
	BA88	L	Н	L	Н	Н	L	L	L	*	*	*	580000h~58FFFFh	2C0000h~2C7FFFh
	BA89	L	Н	L	Н	Н	L	L	Н	*	*	*	590000h~59FFFh	2C8000h~2CFFFFh
	BA90	L	Н	L	Н	Н	L	Н	L	*	*	*	5A0000h~5AFFFFh	2D0000h~2D7FFFh
	BA91	L	Н	L	Ι	Η	L	Η	Η	*	*	*	5B0000h~5BFFFFh	2D8000h~2DFFFFh
	BA92	L	Н	L	Н	Н	Н	L	L	*	*	*	5C0000h~5CFFFh	2E0000h~2E7FFh
	BA93	L	Н	L	Н	Н	Н	L	Н	*	*	*	5D0000h~5DFFFFh	2E8000h~2EFFFFh
	BA94	L	Н	L	Н	Н	Н	Н	L	*	*	*	5E0000h~5EFFFh	2F0000h~2F7FFFh
	BA95	L	Н	L	Н	Н	Н	Н	Н	*	*	*	5F0000h~5FFFFh	2F8000h~2FFFFFh



					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA96	L	Н	Н	L	L	L	L	L	*	*	*	600000h~60FFFh	300000h~307FFFh
	BA97	L	Н	Н	L	L	L	L	Н	*	*	*	610000h~61FFFh	308000h~30FFFFh
	BA98	L	Н	Н	L	L	L	Н	L	*	*	*	620000h~62FFFh	310000h~317FFFh
	BA99	L	Н	Н	L	L	L	Н	Н	*	*	*	630000h~63FFFFh	318000h~31FFFFh
	BA100	L	Н	Н	L	L	Н	L	L	*	*	*	640000h~64FFFh	320000h~327FFFh
	BA101	L	Н	Н	L	L	Н	L	Н	*	*	*	650000h~65FFFFh	328000h~32FFFFh
	BA102	L	Н	Н	L	L	Н	Н	L	*	*	*	660000h~66FFFFh	330000h~337FFFh
	BA103	L	Н	Н	L	L	Н	Н	Н	*	*	*	670000h~67FFFh	338000h~33FFFFh
	BA104	L	Н	Н	L	Н	L	L	L	*	*	*	680000h~68FFFFh	340000h~347FFFh
	BA105	L	Н	Н	L	Н	L	L	Н	*	*	*	690000h~69FFFh	348000h~34FFFFh
	BA106	L	Н	Н	L	Н	L	Н	L	*	*	*	6A0000h~6AFFFh	350000h~357FFFh
	BA107	L	Н	Н	L	Н	L	Н	Н	*	*	*	6B0000h~6BFFFFh	358000h~35FFFFh
	BA108	L	Н	Н	L	Н	Н	L	L	*	*	*	6C0000h~6CFFFh	360000h~367FFFh
	BA109	L	Н	Н	L	Н	Н	L	Н	*	*	*	6D0000h~6DFFFh	368000h~36FFFFh
	BA110	L	Н	Н	L	Н	Н	Н	L	*	*	*	6E0000h~6EFFFh	370000h~377FFFh
BK1	BA111	L	Н	Н	L	Н	Н	Н	Н	*	*	*	6F0000h~6FFFFh	378000h~37FFFFh
BKI	BA112	L	Н	Н	Н	L	L	L	L	*	*	*	700000h~70FFFh	380000h~387FFFh
	BA113	L	Н	Н	Н	L	L	L	Н	*	*	*	710000h~71FFFFh	388000h~38FFFFh
	BA114	L	Η	Η	Η	L	L	Н	L	*	*	*	720000h~72FFFFh	390000h~397FFFh
	BA115	L	Ι	Ι	Ι	Ы	Ы	Ι	Ι	*	*	*	730000h~73FFFFh	398000h~39FFFFh
	BA116	L	Н	Н	Н	L	Н	L	Г	*	*	*	740000h~74FFFFh	3A0000h~3A7FFFh
	BA117	L	Ι	Ι	Ι	Ы	Ι	L	Ι	*	*	*	770000h~75FFFFh	3A8000h~3AFFFFh
	BA118	L	Н	Н	Н	L	Н	Н	Г	*	*	*	760000h~76FFFh	3B0000h~3B7FFFh
	BA119	L	Η	Η	Η	L	Η	Н	Н	*	*	*	770000h~77FFFFh	3B8000h~3BFFFFh
	BA120	L	Ι	Ι	Ι	Ι	Ы	Ы	Ы	*	*	*	780000h~78FFFFh	3C0000h~3C7FFFh
	BA121	L	Н	Н	Н	Н	L	L	I	*	*	*	790000h~79FFFFh	3C8000h~3CFFFFh
	BA122	L	Н	Н	Н	Н	L	Н	L	*	*	*	7A0000h~7AFFFFh	3D0000h~3D7FFFh
	BA123	L	Н	Н	Н	Н	L	Н	Н	*	*	*	7B0000h~7BFFFFh	3D8000h~3DFFFFh
	BA124	L	Н	Н	Н	Н	Н	L	L	*	*	*	7C0000h~7CFFFh	3E0000h~3E7FFh
	BA125	L	Н	Н	Н	Н	Н	L	Η	*	*	*	7D0000h~7DFFFFh	3E8000h~3EFFFFh
	BA126	L	Н	Н	Н	Н	Н	Н	L	*	*	*	7E0000h~7EFFFh	3F0000h~3F7FFFh
	BA127	L	Н	Н	Н	Н	Н	Н	Н	*	*	*	7F0000h~7FFFFh	3F8000h~3FFFFFh

					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE
"	π	A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA128	Н	L	L	L	L	L	L	L	*	*	*	800000h~80FFFh	400000h~407FFFh
	BA129	Н	L	L	L	L	L	L	Н	*	*	*	810000h~81FFFFh	408000h~40FFFFh
	BA130	Н	L	L	L	L	L	Н	L	*	*	*	820000h~82FFFh	410000h~417FFFh
	BA131	Н	L	L	L	L	L	Н	Н	*	*	*	830000h~83FFFFh	418000h~41FFFFh
	BA132	Н	L	L	L	L	Н	L	L	*	*	*	840000h~84FFFFh	420000h~427FFFh
	BA133	Н	L	L	L	L	Н	L	Н	*	*	*	850000h~85FFFFh	428000h~42FFFFh
	BA134	Н	L	L	L	L	Н	Н	L	*	*	*	860000h~86FFFFh	430000h~437FFFh
	BA135	Н	L	L	L	L	Н	Н	Н	*	*	*	870000h~87FFFh	438000h~43FFFFh
	BA136	Н	L	L	L	Н	L	L	L	*	*	*	880000h~88FFFFh	440000h~447FFFh
	BA137	Н	L	L	L	Н	L	L	Н	*	*	*	890000h~89FFFh	448000h~44FFFFh
	BA138	Н	L	L	L	Н	L	Н	L	*	*	*	8A0000h~8AFFFFh	450000h~457FFFh
	BA139	Н	L	L	L	Н	L	Н	Н	*	*	*	8B0000h~8BFFFFh	458000h~45FFFFh
	BA140	Н	L	L	L	Н	Н	L	L	*	*	*	8C0000h~8CFFFh	460000h~467FFFh
	BA141	Н	L	L	L	Н	Н	L	Н	*	*	*	8D0000h~8DFFFFh	468000h~46FFFFh
	BA142	Н	L	L	L	Н	Н	Н	L	*	*	*	8E0000h~8EFFFh	470000h~477FFFh
BK2	BA143	Н	L	L	L	Н	Н	Н	Н	*	*	*	8F0000h~8FFFFh	478000h~47FFFFh
BNZ	BA144	Н	L	L	Н	L	L	L	L	*	*	*	900000h~90FFFh	480000h~487FFFh
	BA145	Н	L	L	Н	L	L	L	Н	*	*	*	910000h~91FFFFh	488000h~48FFFFh
	BA146	Н	L	L	Н	L	L	Н	L	*	*	*	920000h~92FFFh	490000h~497FFFh
	BA147	Н	L	L	Н	L	L	Н	Н	*	*	*	930000h~93FFFFh	498000h~49FFFFh
	BA148	Н	L	L	Н	L	Н	L	L	*	*	*	940000h~94FFFFh	4A0000h~4A7FFFh
	BA149	Н	L	L	Н	L	Н	L	Н	*	*	*	950000h~95FFFh	4A8000h~4AFFFFh
	BA150	Н	L	L	Н	L	Н	Н	L	*	*	*	960000h~96FFFh	4B0000h~4B7FFFh
	BA151	Н	L	L	Н	L	Н	Н	Н	*	*	*	970000h~97FFFh	4B8000h~4BFFFFh
	BA152	Н	L	L	Н	Н	L	L	L	*	*	*	980000h~98FFFFh	4C0000h~4C7FFFh
	BA153	Н	L	L	Н	Н	L	L	Н	*	*	*	990000h~99FFFh	4C8000h~4CFFFFh
	BA154	Н	L	L	Н	Н	L	Н	L	*	*	*	9A0000h~9AFFFh	4D0000h~4D7FFFh
	BA155	Н	L	L	Ι	Η	L	Η	Η	*	*	*	9B0000h~9BFFFFh	4D8000h~4DFFFFh
	BA156	Н	L	L	Н	Н	Н	L	L	*	*	*	9C0000h~9CFFFh	4E0000h~4E7FFh
	BA157	Н	L	L	Ι	Η	Η	L	Η	*	*	*	9D0000h~9DFFFh	4E8000h~4EFFFFh
	BA158	Н	L	L	Ι	Η	Η	Η	L	*	*	*	9E0000h~9EFFFh	4F0000h~4F7FFFh
	BA159	Н	L	L	Н	Н	Н	Н	Н	*	*	*	9F0000h~9FFFFh	4F8000h~4FFFFFh

					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA160	Н	L	Н	L	L	L	L	L	*	*	*	A00000h~A0FFFh	500000h~507FFFh
	BA161	Н	L	Н	L	L	L	L	Н	*	*	*	A10000h~A1FFFFh	508000h~50FFFFh
	BA162	Н	L	Н	L	L	L	Н	L	*	*	*	A20000h~A2FFFFh	510000h~517FFFh
	BA163	Н	L	Н	L	L	L	Н	Н	*	*	*	A30000h~A3FFFFh	518000h~51FFFFh
	BA164	Н	L	Н	L	L	Н	L	L	*	*	*	A40000h~A4FFFFh	520000h~527FFFh
	BA165	Н	L	Н	L	L	Н	L	Н	*	*	*	A50000h~A5FFFFh	528000h~52FFFFh
	BA166	Н	L	Н	L	L	Н	Н	L	*	*	*	A60000h~A6FFFh	530000h~537FFFh
	BA167	Н	L	Н	L	L	Н	Н	Н	*	*	*	A70000h~A7FFFh	538000h~53FFFFh
	BA168	Н	L	Н	L	Н	L	L	L	*	*	*	A80000h~A8FFFFh	540000h~547FFFh
	BA169	Н	L	Н	L	Н	L	L	Н	*	*	*	A90000h~A9FFFh	548000h~54FFFFh
	BA170	Н	L	Н	L	Н	L	Н	L	*	*	*	AA0000h~AAFFFh	550000h~557FFFh
	BA171	Н	L	Н	L	Н	L	Н	Н	*	*	*	AB0000h~ABFFFFh	558000h~55FFFFh
	BA172	Н	L	Н	L	Н	Н	L	L	*	*	*	AC0000h~ACFFFh	560000h~567FFFh
	BA173	Н	L	Н	L	Н	Н	L	Н	*	*	*	AD0000h~ADFFFFh	568000h~56FFFFh
	BA174	Н	L	Н	L	Н	Н	Н	L	*	*	*	AE0000h~AEFFFh	570000h~577FFFh
BK2	BA175	Н	L	Н	L	Н	Н	Н	Н	*	*	*	AF0000h~AFFFFh	578000h~57FFFFh
BKZ	BA176	Н	L	Н	Н	L	L	L	L	*	*	*	B00000h~B0FFFh	580000h~587FFFh
	BA177	Н	L	Н	Н	L	L	L	Н	*	*	*	B10000h~B1FFFFh	588000h~58FFFFh
	BA178	Н	L	Η	Η	L	L	Н	L	*	*	*	B20000h~B2FFFh	590000h~597FFh
	BA179	Н	L	Н	Н	L	L	Н	Н	*	*	*	B30000h~B3FFFFh	598000h~59FFFFh
	BA180	Н	L	Н	Н	L	Н	L	L	*	*	*	B40000h~B4FFFFh	5A0000h~5A7FFFh
	BA181	Н	Ы	Ι	Ι	Ы	Ι	L	Ι	*	*	*	B50000h~B5FFFFh	5A8000h~5AFFFFh
	BA182	Н	L	Н	Н	L	Н	Н	L	*	*	*	B60000h~B6FFFFh	5B0000h~5B7FFFh
	BA183	Н	L	Η	Η	L	Η	Н	Η	*	*	*	B70000h~B7FFFh	5B8000h~5BFFFFh
	BA184	Н	Ы	Ι	Ι	Ι	Ы	L	Ы	*	*	*	B80000h~B8FFFFh	5C0000h~5C7FFFh
	BA185	Н	L	Н	Н	Н	L	L	Н	*	*	*	B90000h~B9FFFh	5C8000h~5CFFFFh
	BA186	Н	L	Н	Н	Н	L	Н	L	*	*	*	BA0000h~BAFFFh	5D0000h~5D7FFFh
	BA187	Н	L	Н	Н	Н	L	Н	Н	*	*	*	BB0000h~BBFFFFh	5D8000h~5DFFFFh
	BA188	Н	L	Н	Н	Н	Н	L	L	*	*	*	BC0000h~BCFFFh	5E0000h~5E7FFh
	BA189	Н	L	Н	Н	Н	Н	L	Н	*	*	*	BD0000h~BDFFFFh	5E8000h~5EFFFFh
	BA190	Н	L	Н	Н	Н	Н	Н	L	*	*	*	BE0000h~BEFFFh	5F0000h~5F7FFFh
	BA191	Н	L	Н	Н	Н	Н	Н	Н	*	*	*	BF0000h~BFFFFh	5F8000h~5FFFFFh

					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA192	Н	Н	L	L	L	L	L	L	*	*	*	C00000h~C0FFFh	600000h~607FFFh
	BA193	Н	Н	L	L	L	L	L	Н	*	*	*	C10000h~C1FFFh	608000h~60FFFFh
	BA194	Н	Н	L	L	L	L	Н	L	*	*	*	C20000h~C2FFFh	610000h~617FFFh
	BA195	Н	Н	L	L	L	L	Н	Н	*	*	*	C30000h~C3FFFh	618000h~61FFFFh
	BA196	Н	Н	L	L	L	Н	L	L	*	*	*	C40000h~C4FFFh	620000h~627FFFh
	BA197	Н	Н	L	L	L	Н	L	Н	*	*	*	C50000h~C5FFFh	628000h~62FFFFh
	BA198	Н	Н	L	L	L	Н	Н	L	*	*	*	C60000h~C6FFFh	630000h~637FFFh
	BA199	Н	Н	L	L	L	Н	Н	Н	*	*	*	C70000h~C7FFFh	638000h~63FFFFh
	BA200	Н	Н	L	L	Н	L	L	L	*	*	*	C80000h~C8FFFh	640000h~647FFFh
	BA201	Н	Н	L	L	Н	L	L	Н	*	*	*	C90000h~C9FFFh	648000h~64FFFFh
	BA202	Н	Н	L	L	Н	L	Н	L	*	*	*	CA0000h~CAFFFh	650000h~657FFFh
	BA203	Н	Н	L	L	Н	L	Н	Н	*	*	*	CB0000h~CBFFFh	658000h~65FFFFh
	BA204	Н	Н	L	L	Н	Н	L	L	*	*	*	CC0000h~CCFFFFh	660000h~667FFFh
	BA205	Н	Н	L	L	Н	Н	L	Н	*	*	*	CD0000h~CDFFFFh	668000h~66FFFFh
	BA206	Н	Н	L	L	Н	Н	Н	L	*	*	*	CE0000h~CEFFFh	670000h~677FFFh
BK2	BA207	Н	Н	L	L	Н	Н	Н	Н	*	*	*	CF0000h~CFFFFh	678000h~67FFFh
BKZ	BA208	Н	Н	L	Н	L	L	L	L	*	*	*	D00000h~D0FFFFh	680000h~687FFFh
	BA209	Н	Н	L	Н	L	L	L	Н	*	*	*	D10000h~D1FFFFh	688000h~68FFFFh
	BA210	Н	Η	L	Η	L	L	Н	L	*	*	*	D20000h~D2FFFh	690000h~697FFFh
	BA211	Н	Ι	Ы	Ι	Ы	Ы	Ι	Ι	*	*	*	D30000h~D3FFFh	698000h~69FFFFh
	BA212	Н	Н	L	Н	L	Н	L	L	*	*	*	D40000h~D4FFFFh	6A0000h~6A7FFFh
	BA213	Н	Ι	Ы	Ι	Ы	Ι	L	Ι	*	*	*	D50000h~D5FFFFh	6A8000h~6AFFFFh
	BA214	Н	Н	L	Н	L	Н	Н	L	*	*	*	D60000h~D6FFFFh	6B0000h~6B7FFFh
	BA215	Н	Η	L	Η	L	Η	Н	Η	*	*	*	D70000h~D7FFFh	6B8000h~6BFFFFh
	BA216	Н	Ι	Ы	Ι	Ι	Ы	Ы	Ы	*	*	*	D80000h~D8FFFFh	6C0000h~6C7FFFh
	BA217	Н	Н	L	Н	Н	L	L	Н	*	*	*	D90000h~D9FFFh	6C8000h~6CFFFh
	BA218	Н	Н	L	Н	Н	L	Н	L	*	*	*	DA0000h~DAFFFFh	6D0000h~6D7FFFh
	BA219	Н	Н	L	Н	Н	L	Н	Н	*	*	*	DB0000h~DBFFFFh	6D8000h~6DFFFFh
	BA220	Н	Н	L	Н	Η	Н	L	L	*	*	*	DC0000h~DCFFFFh	6E0000h~6E7FFh
	BA221	Н	Н	L	Н	Н	Н	L	Н	*	*	*	DD0000h~DDFFFFh	6E8000h~6EFFFFh
	BA222	Н	Н	L	Н	Н	Н	Н	L	*	*	*	DE0000h~DEFFFh	6F0000h~6F7FFh
	BA223	Н	Н	L	Н	Н	Н	Н	Н	*	*	*	DF0000h~DFFFFh	6F8000h~6FFFFh



					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DDRE										ADDRES	S RANGE
"	"	A22	A21		A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA224	Н	Н	Н	L	L	L	L	L	*	*	*	E00000h~E0FFFh	700000h~707FFFh
	BA225	Н	Н	Н	L	L	L	L	Н	*	*	*	E10000h~E1FFFh	708000h~70FFFFh
	BA226	Н	Н	Н	L	L	L	Н	L	*	*	*	E20000h~E2FFFh	710000h~717FFFh
	BA227	Н	Н	Н	L	L	L	Н	Н	*	*	*	E30000h~E3FFFh	718000h~71FFFFh
	BA228	Н	Н	Н	L	L	Н	L	L	*	*	*	E40000h~E4FFFh	720000h~727FFFh
	BA229	Н	Н	Н	L	L	Н	L	Н	*	*	*	E50000h~E5FFFh	728000h~72FFFFh
	BA230	Н	Н	Н	L	L	Н	Н	L	*	*	*	E60000h~E6FFFh	730000h~737FFFh
	BA231	Н	Н	Н	L	L	Н	Н	Н	*	*	*	E70000h~E7FFFh	738000h~73FFFFh
	BA232	Н	Н	Н	L	Н	L	L	L	*	*	*	E80000h~E8FFFh	740000h~747FFFh
	BA233	Н	Н	Н	L	Н	L	L	Н	*	*	*	E90000h~E9FFFh	748000h~74FFFFh
	BA234	Н	Н	Н	L	Н	L	Н	L	*	*	*	EA0000h~EAFFFh	750000h~757FFFh
	BA235	Н	Н	Н	L	Н	L	Н	Н	*	*	*	EB0000h~EBFFFh	758000h~75FFFFh
	BA236	Н	Н	Н	L	Н	Н	L	L	*	*	*	EC0000h~ECFFFh	760000h~767FFFh
	BA237	Н	Н	Н	L	Н	Н	L	Н	*	*	*	ED0000h~EDFFFh	768000h~76FFFFh
	BA238	Н	Н	Н	L	Н	Н	Н	L	*	*	*	EE0000h~EEFFFh	770000h~777FFFh
ВК3	BA239	Н	Н	Н	L	Н	Н	Н	Н	*	*	*	EF0000h~EFFFFh	778000h~77FFFFh
	BA240	Н	Н	Н	Н	L	L	L	L	*	*	*	F00000h~F0FFFh	780000h~787FFFh
	BA241	Н	Н	Н	Н	L	L	L	Н	*	*	*	F10000h~F1FFFh	788000h~78FFFFh
	BA242	Н	Н	Н	Н	L	L	Н	L	*	*	*	F20000h~F2FFFh	790000h~797FFFh
	BA243	Н	Н	Н	Н	L	L	Н	Н	*	*	*	F30000h~F3FFFh	798000h~79FFFFh
	BA244	Н	Н	Н	Н	L	Н	L	L	*	*	*	F40000h~F4FFFh	7A0000h~7A7FFFh
	BA245	Н	Н	Н	Н	L	Н	L	Н	*	*	*	F70000h~F5FFFh	7A8000h~7AFFFFh
	BA246	Н	Н	Н	Н	L	Н	Н	L	*	*	*	F60000h~E6FFFh	7B0000h~7B7FFFh
	BA247	Н	Н	Н	Н	L	Н	Н	Н	*	*	*	F70000h~F7FFFh	7B8000h~7BFFFFh
	BA248	Н	Н	Н	Н	Н	L	L	L	*	*	*	F80000h~F8FFFFh	7C0000h~7C7FFFh
	BA249	Н	Н	Н	Н	Н	L	L	Н	*	*	*	F90000h~F9FFFh	7C8000h~7CFFFFh
	BA250	Н	Н	Н	Н	Н	L	Н	L	*	*	*	FA0000h~FAFFFh	7D0000h~7D7FFFh
	BA251	Н	Н	Н	Н	Н	L	Н	Н	*	*	*	FB0000h~FBFFFFh	7D8000h~7DFFFFh
	BA252	Н	Н	Н	Н	Н	Н	L	L	*	*	*	FC0000h~FCFFFh	7E0000h~7E7FFh
	BA253	Н	Н	Н	Н	Н	Н	L	Н	*	*	*	FD0000h~FDFFFh	7E8000h~7EFFFFh
	BA254	Н	Н	Н	Н	Н	Н	Н	L	*	*	*	FE0000h~FEFFFh	7F0000h~7F7FFFh

					BLC	CK A	DDRE	ESS						
BANK #	BLOCK #		BANK DDRE	-									ADDRES	S RANGE
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA255	Н	Н	Н	Н	Н	Н	Н	Η	L	L	L	FF0000h~FF1FFFh	7F8000h~7F8FFFh
	BA256	Н	Н	Н	Н	Н	Н	Н	Η	L	L	Н	FF2000h~FF3FFFh	7F9000h~7F9FFFh
	BA257	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	L	FF4000h~FF5FFFh	7FA000h~7FAFFFh
BK3	BA258	Н	Н	Н	Н	Н	Н	Н	Η	L	Η	Н	FF6000h~FF7FFh	7FB000h~7FBFFFh
BRS	BA259	Н	Н	Н	Н	Н	Н	Н	Η	Н	L	L	FF8000h~FF9FFFh	7FC000h~7FCFFFh
	BA260	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	FFA000h~FFBFFFh	7FD000h~7FDFFFh
	BA261	Н	Н	Н	Н	Н	Н	Н	Η	Н	Η	L	FFC000h~FFDFFFh	7FE000h~7FEFFFh
	BA262	Н	Н	Н	Н	Н	Н	Н	Η	Н	Η	Н	FFE000h~FFFFFh	7FF000h~7FFFFFh

(2) TC58FVM7B2A (bottom boot block)

BANK	BLOCK		544	,	BLC	CK A	DDRE	ESS					ADDRES:	S RANGE
#	#		BANK DDRE	-										
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA0	L	L	L	L	L	L	L	L	L	L	L	000000h~001FFFh	000000h~000FFFh
	BA1	L	L	L	L	L	L	L	L	L	L	Н	002000h~003FFFh	001000h~001FFFh
	BA2	L	L	L	L	L	L	L	L	L	Н	L	004000h~005FFFh	002000h~002FFFh
BK0	BA3	L	L	L	L	L	L	L	L	L	Н	Н	006000h~007FFFh	003000h~003FFFh
Bito	BA4	L	L	L	L	L	L	L	L	Н	L	L	008000h~009FFFh	004000h~004FFFh
	BA5	L	L	L	L	L	L	L	L	Ι	L	Н	00A000h~00BFFFh	005000h~005FFFh
	BA6	L	L	L	L	L	L	L	L	Η	Н	L	00C000h~00DFFFh	006000h~006FFFh
	BA7	L	L	L	L	L	L	L	L	Η	Н	Н	00E000h~00FFFFh	007000h~007FFFh



					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DDRE										ADDRES	S RANGE
<i>"</i>	π	A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA8	L	L	L	L	L	L	L	Н	*	*	*	010000h~01FFFFh	008000h~00FFFFh
	BA9	L	L	L	L	L	L	Н	L	*	*	*	020000h~02FFFFh	010000h~017FFFh
	BA10	L	L	L	L	L	L	Н	Н	*	*	*	030000h~03FFFFh	018000h~01FFFFh
	BA11	L	L	L	L	L	Н	L	L	*	*	*	040000h~04FFFFh	020000h~027FFFh
	BA12	L	L	L	L	L	Н	L	Н	*	*	*	050000h~05FFFFh	028000h~02FFFFh
	BA13	L	L	L	L	L	Н	Н	L	*	*	*	060000h~06FFFFh	030000h~037FFFh
	BA14	L	L	L	L	L	Н	Н	Н	*	*	*	070000h~07FFFh	038000h~03FFFFh
	BA15	L	L	L	L	Н	L	L	L	*	*	*	080000h~08FFFFh	040000h~047FFFh
	BA16	L	L	L	L	Н	L	L	Н	*	*	*	090000h~09FFFFh	048000h~04FFFFh
	BA17	L	L	L	L	Н	L	Н	L	*	*	*	0A0000h~0AFFFh	050000h~057FFFh
	BA18	L	L	L	L	Н	L	Н	Н	*	*	*	0B0000h~0BFFFFh	058000h~05FFFFh
	BA19	L	L	L	L	Н	Н	L	L	*	*	*	0C0000h~0CFFFh	060000h~067FFFh
	BA20	L	L	L	L	Н	Н	L	Н	*	*	*	0D0000h~0DFFFh	068000h~06FFFFh
	BA21	L	L	L	L	Н	Н	Н	L	*	*	*	0E0000h~0EFFFh	070000h~077FFFh
	BA22	L	L	L	L	Н	Н	Н	Н	*	*	*	0F0000h~0FFFFh	078000h~07FFFFh
ВК0	BA23	L	L	L	Н	L	L	L	L	*	*	*	100000h~10FFFFh	080000h~087FFFh
	BA24	L	L	L	Н	L	L	L	Н	*	*	*	110000h~11FFFFh	088000h~08FFFFh
	BA25	L	L	L	Н	L	L	Н	L	*	*	*	120000h~12FFFFh	090000h~097FFFh
	BA26	L	L	L	Н	L	L	Н	Н	*	*	*	130000h~13FFFFh	098000h~09FFFFh
	BA27	L	L	L	Н	L	Н	L	L	*	*	*	140000h~14FFFFh	0A0000h~0A7FFFh
	BA28	L	L	L	Н	L	Н	L	Н	*	*	*	150000h~15FFFFh	0A8000h~0AFFFFh
	BA29	L	L	L	Н	L	Н	Н	L	*	*	*	160000h~16FFFFh	0B0000h~0B7FFFh
	BA30	L	L	L	Н	L	Н	Н	Н	*	*	*	170000h~17FFFFh	0B8000h~0BFFFFh
	BA31	L	L	L	Н	Н	L	L	L	*	*	*	180000h~18FFFFh	0C0000h~0C7FFFh
	BA32	L	L	L	Н	Н	L	L	Н	*	*	*	190000h~19FFFFh	0C8000h~0CFFFFh
	BA33	L	L	L	Н	Н	L	Н	L	*	*	*	1A0000h~1AFFFFh	0D0000h~0D7FFFh
	BA34	L	L	L	Н	Н	L	Н	Н	*	*	*	1B0000h~1BFFFFh	0D8000h~0DFFFFh
	BA35	L	L	L	Н	Н	Н	L	L	*	*	*	1C0000h~1CFFFh	0E0000h~0E7FFh
	BA36	L	L	L	Н	Н	Н	L	Н	*	*	*	1D0000h~1DFFFFh	0E8000h~0EFFFh
	BA37	L	L	L	Н	Н	Н	Н	L	*	*	*	1E0000h~1EFFFFh	0F0000h~0F7FFFh
	BA38	L	L	L	Н	Н	Н	Н	Н	*	*	*	1F0000h~1FFFFFh	0F8000h~0FFFFh

BANK	BLOCK		BANK		BLC	OCK A	DDRE	SS					ADDRES	S RANGE
#	#	A22	DRES	SS A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA39	L	L	Н	L	L	L	L	L	*	*	*	200000h~20FFFFh	100000h~107FFFh
	BA40	L	L	Н	L	L	L	L	Н	*	*	*	210000h~21FFFFh	108000h~10FFFFh
	BA41	L	L	Н	L	L	L	Н	L	*	*	*	220000h~22FFFFh	110000h~117FFFh
	BA42	L	L	Н	L	L	L	Н	Н	*	*	*	230000h~23FFFFh	118000h~11FFFFh
	BA43	L	L	Н	L	L	Н	L	L	*	*	*	240000h~24FFFFh	120000h~127FFFh
	BA44	L	L	Н	L	L	Н	L	Н	*	*	*	250000h~25FFFFh	128000h~12FFFFh
	BA45	L	L	Н	L	L	Н	Н	L	*	*	*	260000h~26FFFh	130000h~137FFFh
	BA46	L	L	Н	L	L	Н	Н	Н	*	*	*	270000h~27FFFh	138000h~13FFFFh
	BA47	L	L	Н	L	Н	L	L	L	*	*	*	280000h~28FFFFh	140000h~147FFFh
	BA48	L	L	Н	L	Н	L	L	Н	*	*	*	290000h~29FFFFh	148000h~14FFFFh
	BA49	L	L	Н	L	Н	L	Н	L	*	*	*	2A0000h~2AFFFFh	150000h~157FFFh
	BA50	L	L	Н	L	Н	L	Н	Н	*	*	*	2B0000h~2BFFFFh	158000h~15FFFFh
	BA51	L	L	Н	L	Н	Н	L	L	*	*	*	2C0000h~2CFFFh	160000h~167FFFh
	BA52	L	L	Н	L	Н	Н	L	Н	*	*	*	2D0000h~2DFFFFh	168000h~16FFFFh
	BA53	L	L	Н	L	Н	Н	Н	L	*	*	*	2E0000h~2EFFFFh	170000h~177FFFh
B144	BA54	L	L	Н	L	Н	Н	Н	Н	*	*	*	2F0000h~2FFFFh	178000h~17FFFFh
BK1	BA55	L	L	Н	Н	L	L	L	L	*	*	*	300000h~30FFFFh	180000h~187FFFh
	BA56	L	L	Н	Н	L	L	L	Н	*	*	*	310000h~31FFFFh	188000h~18FFFFh
	BA57	L	L	Н	Н	L	L	Н	L	*	*	*	320000h~32FFFFh	190000h~197FFFh
	BA58	L	L	Н	Н	L	L	Н	Н	*	*	*	330000h~33FFFFh	198000h~19FFFFh
	BA59	L	L	Н	Н	L	Н	L	L	*	*	*	340000h~34FFFFh	1A0000h~1A7FFFh
	BA60	L	L	Н	Н	L	Н	L	Н	*	*	*	350000h~35FFFFh	1A8000h~1AFFFFh
	BA61	L	L	Н	Н	L	Н	Н	L	*	*	*	360000h~36FFFFh	1B0000h~1B7FFFh
	BA62	L	L	Н	Н	L	Н	Н	Н	*	*	*	370000h~37FFFFh	1B8000h~1BFFFFh
	BA63	L	L	Н	Н	Н	L	L	L	*	*	*	380000h~38FFFFh	1C0000h~1C7FFFh
	BA64	L	L	Н	Н	Н	L	L	Н	*	*	*	390000h~39FFFFh	1C8000h~1CFFFFh
	BA65	L	L	Н	Η	Н	L	Н	L	*	*	*	3A0000h~3AFFFh	1D0000h~1D7FFFh
	BA66	L	L	Н	Η	Н	L	Н	Н	*	*	*	3B0000h~3BFFFFh	1D8000h~1DFFFFh
	BA67	L	L	Н	Η	Н	Н	L	L	*	*	*	3C0000h~3CFFFh	1E0000h~1E7FFFh
	BA68	L	L	Н	Н	Н	Н	L	Н	*	*	*	3D0000h~3DFFFFh	1E8000h~1EFFFFh
	BA69	L	L	Н	Н	Н	Н	Н	L	*	*	*	3E0000h~3EFFFh	1F0000h~1F7FFFh
	BA70	L	L	Н	Н	Н	Н	Н	Н	*	*	*	3F0000h~3FFFFh	1F8000h~1FFFFh

					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DDRE										ADDRES	S RANGE
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA71	L	Н	L	L	L	L	L	L	*	*	*	400000h~40FFFFh	200000h~207FFFh
	BA72	L	Н	L	L	L	L	L	Н	*	*	*	410000h~41FFFFh	208000h~20FFFFh
	BA73	L	Н	L	L	L	L	Н	L	*	*	*	420000h~42FFFFh	210000h~217FFFh
	BA74	L	Н	L	L	L	L	Н	Н	*	*	*	430000h~43FFFFh	218000h~21FFFFh
	BA75	L	Н	L	L	L	Н	L	L	*	*	*	440000h~44FFFFh	220000h~227FFFh
	BA76	L	Н	L	L	L	Η	L	Н	*	*	*	450000h~45FFFFh	228000h~22FFFFh
	BA77	L	Н	L	L	L	Η	Н	L	*	*	*	460000h~46FFFh	230000h~237FFFh
	BA78	L	Н	L	Ы	L	Ι	Ι	Ι	*	*	*	470000h~47FFFFh	238000h~23FFFFh
	BA79	L	Н	L	L	Н	L	L	L	*	*	*	480000h~48FFFFh	240000h~247FFFh
	BA80	L	Н	L	L	Η	L	L	Η	*	*	*	490000h~49FFFFh	248000h~24FFFFh
	BA81	L	Н	L	L	Н	L	Н	L	*	*	*	4A0000h~4AFFFFh	250000h~257FFFh
	BA82	L	Н	L	L	Η	L	Η	Η	*	*	*	4B0000h~4BFFFFh	258000h~25FFFFh
	BA83	L	Н	L	L	Н	Н	L	L	*	*	*	4C0000h~4CFFFh	260000h~267FFFh
	BA84	L	Н	L	L	Н	Н	L	Н	*	*	*	4D0000h~4DFFFFh	268000h~26FFFFh
	BA85	L	Н	L	L	Н	Н	Н	L	*	*	*	4E0000h~4EFFFFh	270000h~277FFFh
BK1	BA86	L	Н	L	L	Н	Н	Н	Н	*	*	*	4F0000h~4FFFFh	278000h~27FFFh
BICT	BA87	L	Н	L	Н	L	L	L	L	*	*	*	500000h~50FFFh	280000h~287FFFh
	BA88	L	Н	L	Ι	L	Ы	L	Ι	*	*	*	510000h~51FFFFh	288000h~28FFFFh
	BA89	L	Н	L	Н	L	L	Н	L	*	*	*	520000h~52FFFFh	290000h~297FFh
	BA90	L	Н	L	Н	L	L	Н	Н	*	*	*	530000h~53FFFFh	298000h~29FFFh
	BA91	L	Н	L	Н	L	Н	L	L	*	*	*	540000h~54FFFFh	2A0000h~2A7FFFh
	BA92	L	Н	L	Н	L	Н	L	Н	*	*	*	550000h~55FFFFh	2A8000h~2AFFFFh
	BA93	L	Н	L	Ι	L	Ι	Ι	Ы	*	*	*	560000h~56FFFFh	2B0000h~2B7FFFh
	BA94	L	Н	L	Η	L	Η	Η	Η	*	*	*	570000h~57FFFh	2B8000h~2BFFFFh
	BA95	L	Н	L	Ι	Ι	L	L	L	*	*	*	580000h~58FFFFh	2C0000h~2C7FFFh
	BA96	L	Н	L	Н	Н	L	L	Н	*	*	*	590000h~59FFFh	2C8000h~2CFFFFh
	BA97	L	Н	L	Н	Н	L	Н	L	*	*	*	5A0000h~5AFFFh	2D0000h~2D7FFFh
	BA98	L	Н	L	Н	Н	L	Н	Н	*	*	*	5B0000h~5BFFFFh	2D8000h~2DFFFFh
	BA99	L	Н	L	Н	Н	Н	L	L	*	*	*	5C0000h~5CFFFh	2E0000h~2E7FFh
	BA100	L	Н	L	Н	Н	Н	L	Н	*	*	*	5D0000h~5DFFFFh	2E8000h~2EFFFFh
	BA101	L	Н	L	Н	Н	Н	Н	L	*	*	*	5E0000h~5EFFFh	2F0000h~2F7FFFh
	BA102	L	Н	L	Н	Н	Н	Н	Н	*	*	*	5F0000h~5FFFFh	2F8000h~2FFFFh

					BLC	CK A	DDRE	SS					400050	ADDRESS RANGE	
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE	
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE	
	BA103	L	Н	Н	L	L	L	L	L	*	*	*	600000h~60FFFh	300000h~307FFFh	
	BA104	L	Н	Н	L	L	L	L	Н	*	*	*	610000h~61FFFFh	308000h~30FFFFh	
	BA105	L	Н	Н	L	L	L	Н	L	*	*	*	620000h~62FFFh	310000h~317FFFh	
	BA106	L	Н	Н	L	L	L	Н	Н	*	*	*	630000h~63FFFFh	318000h~31FFFFh	
	BA107	L	Н	Н	L	L	Н	L	L	*	*	*	640000h~64FFFh	320000h~327FFFh	
	BA108	L	Н	Н	L	L	Н	L	Н	*	*	*	650000h~65FFFh	328000h~32FFFFh	
	BA109	L	Н	Н	L	L	Н	Н	L	*	*	*	660000h~66FFFFh	330000h~337FFFh	
	BA110	L	Н	Н	L	L	Н	Н	Н	*	*	*	670000h~67FFFh	338000h~33FFFFh	
	BA111	L	Н	Н	L	Н	L	L	L	*	*	*	680000h~68FFFFh	340000h~347FFFh	
	BA112	L	Н	Н	L	Н	L	L	Н	*	*	*	690000h~69FFFh	348000h~34FFFFh	
	BA113	L	Н	Н	L	Н	L	Н	L	*	*	*	6A0000h~6AFFFh	350000h~357FFFh	
	BA114	L	Η	Н	L	Н	L	Н	Н	*	*	*	6B0000h~6BFFFFh	358000h~35FFFFh	
	BA115	L	Η	Н	L	Η	Η	L	L	*	*	*	6C0000h~6CFFFh	360000h~367FFFh	
	BA116	L	Н	Ι	L	Н	Н	L	Н	*	*	*	6D0000h~6DFFFFh	368000h~36FFFFh	
	BA117	L	Η	Н	L	Н	Η	Н	L	*	*	*	6E0000h~6EFFFh	370000h~377FFFh	
BK1	BA118	L	Η	Н	L	Н	Η	Н	Н	*	*	*	6F0000h~6FFFFh	378000h~37FFFFh	
DICT	BA119	L	Н	Ι	Н	L	L	L	L	*	*	*	700000h~70FFFFh	380000h~387FFFh	
	BA120	L	Ι	Η	Ι	L	Ы	L	Ι	*	*	*	710000h~71FFFFh	388000h~38FFFFh	
	BA121	L	Н	Н	Н	L	L	Н	L	*	*	*	720000h~72FFFh	390000h~397FFFh	
	BA122	L	Ι	Η	Ι	L	Ы	Ι	Ι	*	*	*	730000h~73FFFFh	398000h~39FFFFh	
	BA123	L	Ι	Η	Ι	L	Ι	L	Ы	*	*	*	740000h~74FFFFh	3A0000h~3A7FFFh	
	BA124	L	Н	Ι	Н	L	Н	L	Н	*	*	*	770000h~75FFFFh	3A8000h~3AFFFFh	
	BA125	L	Н	Н	Н	L	Н	Н	L	*	*	*	760000h~76FFFh	3B0000h~3B7FFFh	
	BA126	L	Н	Н	Н	L	Н	Н	Н	*	*	*	770000h~77FFFFh	3B8000h~3BFFFFh	
	BA127	L	Н	Н	Н	Н	L	L	L	*	*	*	780000h~78FFFFh	3C0000h~3C7FFFh	
	BA128	L	Н	Н	Н	Н	L	L	Н	*	*	*	790000h~79FFFh	3C8000h~3CFFFFh	
	BA129	L	Н	Н	Н	Н	L	Н	L	*	*	*	7A0000h~7AFFFFh	3D0000h~3D7FFFh	
	BA130	L	Н	Н	Н	Н	L	Н	Н	*	*	*	7B0000h~7BFFFFh	3D8000h~3DFFFFh	
	BA131	L	Н	Н	Н	Н	Н	L	L	*	*	*	7C0000h~7CFFFh	3E0000h~3E7FFFh	
	BA132	L	Η	Η	Ι	Η	Η	L	Η	*	*	*	7D0000h~7DFFFFh	3E8000h~3EFFFFh	
	BA133	L	Н	Н	Н	Н	Н	Н	L	*	*	*	7E0000h~7EFFFh	3F0000h~3F7FFFh	
	BA134	L	Н	Н	Н	Н	Н	Н	Н	*	*	*	7F0000h~7FFFFh	3F8000h~3FFFFFh	

					BLC	CK A	DDRE	SS						ADDRESS RANGE	
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE	
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE	
	BA135	Н	L	L	L	L	L	L	L	*	*	*	800000h~80FFFFh	400000h~407FFFh	
	BA136	Н	L	L	L	L	L	L	Н	*	*	*	810000h~81FFFFh	408000h~40FFFFh	
	BA137	Н	L	L	L	L	L	Н	L	*	*	*	820000h~82FFFFh	410000h~417FFFh	
	BA138	Н	L	L	L	L	L	Н	Н	*	*	*	830000h~83FFFFh	418000h~41FFFFh	
	BA139	Н	L	L	L	L	Н	L	L	*	*	*	840000h~84FFFFh	420000h~427FFFh	
	BA140	Н	L	L	L	L	Н	L	Н	*	*	*	850000h~85FFFFh	428000h~42FFFFh	
	BA141	Н	L	L	L	L	Н	Н	L	*	*	*	860000h~86FFFFh	430000h~437FFFh	
	BA142	Н	L	L	L	L	Н	Н	Н	*	*	*	870000h~87FFFh	438000h~43FFFFh	
	BA143	Н	L	L	L	Н	L	L	L	*	*	*	880000h~88FFFFh	440000h~447FFFh	
	BA144	Н	L	L	L	Н	L	L	Н	*	*	*	890000h~89FFFFh	448000h~44FFFFh	
	BA145	Н	L	L	L	Н	L	Н	L	*	*	*	8A0000h~8AFFFh	450000h~457FFFh	
	BA146	Н	L	L	L	Н	L	Н	Н	*	*	*	8B0000h~8BFFFFh	458000h~45FFFFh	
	BA147	Н	L	L	L	Н	Н	L	L	*	*	*	8C0000h~8CFFFh	460000h~467FFFh	
	BA148	Н	L	L	L	Н	Н	L	Н	*	*	*	8D0000h~8DFFFFh	468000h~46FFFFh	
	BA149	Н	L	L	L	Н	Н	Н	L	*	*	*	8E0000h~8EFFFFh	470000h~477FFFh	
BK2	BA150	Н	L	L	L	Н	Н	Н	Н	*	*	*	8F0000h~8FFFFh	478000h~47FFFFh	
BNZ	BA151	Н	L	L	Н	L	L	L	L	*	*	*	900000h~90FFFh	480000h~487FFFh	
	BA152	Н	L	L	Н	L	L	L	Н	*	*	*	910000h~91FFFFh	488000h~48FFFFh	
	BA153	Н	L	L	Н	L	L	Н	L	*	*	*	920000h~92FFFFh	490000h~497FFFh	
	BA154	Н	L	L	Н	L	L	Н	Н	*	*	*	930000h~93FFFFh	498000h~49FFFFh	
	BA155	Н	L	L	Н	L	Н	L	L	*	*	*	940000h~94FFFFh	4A0000h~4A7FFFh	
	BA156	Н	L	L	Н	L	Н	L	Н	*	*	*	950000h~95FFFh	4A8000h~4AFFFFh	
	BA157	Н	L	L	Н	L	Н	Н	L	*	*	*	960000h~96FFFh	4B0000h~4B7FFFh	
	BA158	Н	L	L	Н	L	Н	Н	Н	*	*	*	970000h~97FFFh	4B8000h~4BFFFFh	
	BA159	Н	L	L	Н	Н	L	L	L	*	*	*	980000h~98FFFFh	4C0000h~4C7FFFh	
	BA160	Н	L	L	Н	Н	L	L	Н	*	*	*	990000h~99FFFh	4C8000h~4CFFFh	
	BA161	Н	L	L	Н	Н	L	Н	L	*	*	*	9A0000h~9AFFFh	4D0000h~4D7FFFh	
	BA162	Н	L	L	Н	Н	L	Н	Н	*	*	*	9B0000h~9BFFFFh	4D8000h~4DFFFFh	
	BA163	Н	L	L	Н	Н	Н	L	L	*	*	*	9C0000h~9CFFFh	4E0000h~4E7FFh	
	BA164	Н	L	L	Н	Н	Н	L	Н	*	*	*	9D0000h~9DFFFFh	4E8000h~4EFFFFh	
	BA165	Н	L	L	Н	Н	Н	Н	L	*	*	*	9E0000h~9EFFFh	4F0000h~4F7FFFh	
	BA166	Н	L	L	Н	Н	Н	Н	Н	*	*	*	9F0000h~9FFFFh	4F8000h~4FFFFh	

					BLC	CK A	DDRE	SS						ADDRESS RANGE	
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE	
		A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE	
	BA167	Н	L	Н	L	L	L	L	L	*	*	*	A00000h~A0FFFh	500000h~507FFFh	
	BA168	Н	L	Н	L	L	L	L	Н	*	*	*	A10000h~A1FFFFh	508000h~50FFFFh	
	BA169	Н	L	Н	L	L	L	Н	L	*	*	*	A20000h~A2FFFh	510000h~517FFFh	
	BA170	Н	L	Н	L	L	L	Н	Н	*	*	*	A30000h~A3FFFh	518000h~51FFFFh	
	BA171	Н	L	Н	L	L	Н	L	L	*	*	*	A40000h~A4FFFFh	520000h~527FFFh	
	BA172	Н	L	Н	L	L	Н	L	Н	*	*	*	A50000h~A5FFFh	528000h~52FFFFh	
	BA173	Н	L	Н	L	L	Н	Н	L	*	*	*	A60000h~A6FFFh	530000h~537FFFh	
	BA174	Н	L	Н	L	L	Н	Н	Н	*	*	*	A70000h~A7FFFh	538000h~53FFFFh	
	BA175	Н	L	Н	L	Н	L	L	L	*	*	*	A80000h~A8FFFFh	540000h~547FFFh	
	BA176	Н	L	Н	L	Н	L	L	Н	*	*	*	A90000h~A9FFFh	548000h~54FFFFh	
	BA177	Н	L	Н	L	Н	L	Н	L	*	*	*	AA0000h~AAFFFh	550000h~557FFFh	
	BA178	Н	L	Н	L	Н	L	Н	Н	*	*	*	AB0000h~ABFFFFh	558000h~55FFFFh	
	BA179	Н	L	Н	L	Η	Η	L	L	*	*	*	AC0000h~ACFFFh	560000h~567FFFh	
	BA180	Η	L	Н	L	Н	Н	L	Н	*	*	*	AD0000h~ADFFFFh	568000h~56FFFFh	
	BA181	Н	L	Н	L	Н	Η	Н	L	*	*	*	AE0000h~AEFFFh	570000h~577FFFh	
BK2	BA182	Н	L	Н	L	Н	Н	Н	Н	*	*	*	AF0000h~AFFFFh	578000h~57FFFFh	
DIVE	BA183	Η	L	Н	Н	L	L	L	L	*	*	*	B00000h~B0FFFh	580000h~587FFFh	
	BA184	Н	Ы	Н	Ι	L	Ы	L	Н	*	*	*	B10000h~B1FFFFh	588000h~58FFFFh	
	BA185	Н	L	Н	Н	L	L	Н	L	*	*	*	B20000h~B2FFFFh	590000h~597FFh	
	BA186	Н	Ы	Н	Ι	L	Ы	Н	Н	*	*	*	B30000h~B3FFFFh	598000h~59FFFFh	
	BA187	Н	Ы	Н	Ι	L	Ι	L	L	*	*	*	B40000h~B4FFFFh	5A0000h~5A7FFFh	
	BA188	Η	L	Н	Н	L	Н	L	Н	*	*	*	B50000h~B5FFFFh	5A8000h~5AFFFFh	
	BA189	Н	L	Н	Н	L	Н	Н	L	*	*	*	B60000h~B6FFFFh	5B0000h~5B7FFFh	
	BA190	Н	L	Н	Н	L	Н	Н	Н	*	*	*	B70000h~B7FFFh	5B8000h~5BFFFFh	
	BA191	Н	L	Н	Н	Н	L	L	L	*	*	*	B80000h~B8FFFFh	5C0000h~5C7FFFh	
	BA192	Н	L	Н	Н	Н	L	L	Н	*	*	*	B90000h~B9FFFh	5C8000h~5CFFFh	
	BA193	Н	L	Н	Н	Н	L	Н	L	*	*	*	BA0000h~BAFFFFh	5D0000h~5D7FFFh	
	BA194	Н	L	Н	Н	Н	L	Н	Н	*	*	*	BB0000h~BBFFFFh	5D8000h~5DFFFFh	
	BA195	Н	L	Н	Н	Н	Н	L	L	*	*	*	BC0000h~BCFFFh	5E0000h~5E7FFh	
	BA196	Н	L	Н	Н	Н	Н	L	Н	*	*	*	BD0000h~BDFFFFh	5E8000h~5EFFFFh	
	BA197	Н	L	Н	Н	Н	Н	Н	L	*	*	*	BE0000h~BEFFFh	5F0000h~5F7FFFh	
	BA198	Н	L	Н	Н	Н	Н	Н	Н	*	*	*	BF0000h~BFFFFh	5F8000h~5FFFFFh	

					BLC	CK A	DDRE	SS					ADDRESS RANGE	
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE
	:	A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA199	Н	Н	L	L	L	L	L	L	*	*	*	C00000h~C0FFFh	600000h~607FFFh
	BA200	Н	Н	L	L	L	L	L	Н	*	*	*	C10000h~C1FFFh	608000h~60FFFFh
	BA201	Н	Н	L	L	L	L	Н	L	*	*	*	C20000h~C2FFFh	610000h~617FFFh
	BA202	Н	Н	L	L	L	L	Н	Н	*	*	*	C30000h~C3FFFh	618000h~61FFFFh
	BA203	Н	Н	L	L	L	Н	L	L	*	*	*	C40000h~C4FFFh	620000h~627FFFh
	BA204	Н	Н	L	L	L	Н	L	Н	*	*	*	C50000h~C5FFFh	628000h~62FFFFh
	BA205	Н	Н	L	L	L	Н	Н	L	*	*	*	C60000h~C6FFFh	630000h~637FFFh
	BA206	Н	Н	L	L	L	Н	Н	Н	*	*	*	C70000h~C7FFFh	638000h~63FFFFh
	BA207	Н	Н	L	L	Н	L	L	L	*	*	*	C80000h~C8FFFh	640000h~647FFFh
	BA208	Н	Н	L	L	Н	L	L	Н	*	*	*	C90000h~C9FFFh	648000h~64FFFFh
	BA209	Н	Н	L	L	Н	L	Н	L	*	*	*	CA0000h~CAFFFh	650000h~657FFFh
	BA210	Н	Н	L	L	Н	L	Н	Н	*	*	*	CB0000h~CBFFFh	658000h~65FFFFh
	BA211	Н	Н	L	L	Н	Н	L	L	*	*	*	CC0000h~CCFFFFh	660000h~667FFFh
	BA212	Н	Н	L	L	Н	Н	L	Н	*	*	*	CD0000h~CDFFFh	668000h~66FFFFh
	BA213	Н	Н	L	L	Н	Н	Н	L	*	*	*	CE0000h~CEFFFh	670000h~677FFFh
BK2	BA214	Н	Н	L	L	Н	Н	Н	Н	*	*	*	CF0000h~CFFFFh	678000h~67FFFh
BNZ	BA215	Н	Н	L	Н	L	L	L	L	*	*	*	D00000h~D0FFFh	680000h~687FFFh
	BA216	Н	Н	L	Н	L	L	L	Н	*	*	*	D10000h~D1FFFFh	688000h~68FFFFh
	BA217	Н	Н	L	Н	L	L	Н	L	*	*	*	D20000h~D2FFFh	690000h~697FFFh
	BA218	Н	Н	L	Н	L	L	Н	Н	*	*	*	D30000h~D3FFFFh	698000h~69FFFh
	BA219	Н	Н	L	Н	L	Н	L	L	*	*	*	D40000h~D4FFFh	6A0000h~6A7FFFh
	BA220	Н	Н	L	Н	L	Н	L	Н	*	*	*	D50000h~D5FFFFh	6A8000h~6AFFFh
	BA221	Н	Н	L	Н	L	Н	Н	L	*	*	*	D60000h~D6FFFFh	6B0000h~6B7FFFh
	BA222	Н	Н	L	Н	L	Н	Н	Н	*	*	*	D70000h~D7FFFh	6B8000h~6BFFFFh
	BA223	Н	Н	L	Н	Н	L	L	L	*	*	*	D80000h~D8FFFFh	6C0000h~6C7FFFh
	BA224	Н	Н	L	Н	Н	L	L	Н	*	*	*	D90000h~D9FFFFh	6C8000h~6CFFFh
	BA225	Н	Н	L	Н	Н	L	Н	L	*	*	*	DA0000h~DAFFFFh	6D0000h~6D7FFFh
	BA226	Н	Н	L	Н	Н	L	Н	Н	*	*	*	DB0000h~DBFFFFh	6D8000h~6DFFFFh
	BA227	Н	Н	L	Н	Н	Н	L	L	*	*	*	DC0000h~DCFFFh	6E0000h~6E7FFh
	BA228	Н	Н	L	Н	Н	Н	L	Н	*	*	*	DD0000h~DDFFFFh	6E8000h~6EFFFh
	BA229	Н	Н	L	Н	Н	Н	Н	L	*	*	*	DE0000h~DEFFFh	6F0000h~6F7FFh
	BA230	Н	Н	L	Н	Н	Н	Н	Н	*	*	*	DF0000h~DFFFFh	6F8000h~6FFFFh

					BLC	CK A	DDRE	SS						
BANK #	BLOCK #		BANK DRE										ADDRES	S RANGE
, ,	,,	A22	A21	A20	A19	A18	A17	A16	A15	A14	A13	A12	BYTE MODE	WORD MODE
	BA231	Н	Н	Н	L	L	L	L	L	*	*	*	E00000h~E0FFFh	700000h~707FFFh
	BA232	Н	Н	Н	L	L	L	L	Н	*	*	*	E10000h~E1FFFh	708000h~70FFFFh
	BA233	Н	Н	Н	L	L	L	Н	L	*	*	*	E20000h~E2FFFh	710000h~717FFFh
	BA234	Н	Н	Н	L	L	L	Н	Н	*	*	*	E30000h~E3FFFh	718000h~71FFFFh
	BA235	Н	Н	Н	L	L	Н	L	L	*	*	*	E40000h~E4FFFh	720000h~727FFFh
	BA236	Н	Н	Н	L	L	Н	L	Н	*	*	*	E50000h~E5FFFh	728000h~72FFFFh
	BA237	Н	Н	Н	L	L	Н	Н	L	*	*	*	E60000h~E6FFFh	730000h~737FFFh
	BA238	Н	Н	Н	L	L	Н	Н	Н	*	*	*	E70000h~E7FFFh	738000h~73FFFFh
	BA239	Н	Н	Н	L	Н	L	L	L	*	*	*	E80000h~E8FFFh	740000h~747FFFh
	BA240	Н	Н	Н	L	Н	L	L	Н	*	*	*	E90000h~E9FFFh	748000h~74FFFFh
	BA241	Н	Н	Н	L	Н	L	Н	L	*	*	*	EA0000h~EAFFFh	750000h~757FFFh
	BA242	Н	Η	Н	L	Н	L	Н	Н	*	*	*	EB0000h~EBFFFh	758000h~75FFFFh
	BA243	Н	Ι	Ι	Ш	Ι	Ι	Ш	Ш	*	*	*	EC0000h~ECFFFh	760000h~767FFFh
	BA244	Н	Н	Ι	L	Н	Н	L	Н	*	*	*	ED0000h~EDFFFh	768000h~76FFFFh
	BA245	Н	Η	Н	L	Н	Η	Н	L	*	*	*	EE0000h~EEFFFh	770000h~777FFFh
BK3	BA246	Н	Н	Н	L	Н	Н	Н	Н	*	*	*	EF0000h~EFFFFh	778000h~77FFFFh
БК	BA247	Н	Н	Ι	Н	L	L	L	L	*	*	*	F00000h~F0FFFh	780000h~787FFFh
	BA248	Н	Ι	Η	Ι	L	Ы	L	Ι	*	*	*	F10000h~F1FFFFh	788000h~78FFFFh
	BA249	Н	Н	Н	Н	L	L	Н	L	*	*	*	F20000h~F2FFFh	790000h~797FFFh
	BA250	Н	Ι	Η	Ι	L	Ы	Ι	Ι	*	*	*	F30000h~F3FFFh	798000h~79FFFFh
	BA251	Н	Ι	Η	Ι	L	Ι	L	Ы	*	*	*	F40000h~F4FFFh	7A0000h~7A7FFFh
	BA252	Н	Н	Ι	Н	L	Н	L	Н	*	*	*	F70000h~F5FFFh	7A8000h~7AFFFFh
	BA253	Н	Н	Н	Н	L	Н	Н	L	*	*	*	F60000h~F6FFFh	7B0000h~7B7FFFh
	BA254	Н	Н	Н	Н	L	Н	Н	Н	*	*	*	F70000h~F7FFFh	7B8000h~7BFFFFh
	BA255	Н	Н	Н	Н	Н	L	L	L	*	*	*	F80000h~F8FFFh	7C0000h~7C7FFFh
	BA256	Н	Н	Н	Н	Н	L	L	Н	*	*	*	F90000h~F9FFFh	7C8000h~7CFFFFh
	BA257	Н	Н	Н	Н	Н	L	Н	L	*	*	*	FA0000h~FAFFFh	7D0000h~7D7FFFh
	BA258	Н	Н	Н	Н	Н	L	Н	Н	*	*	*	FB0000h~FBFFFFh	7D8000h~7DFFFFh
	BA259	Н	Н	Н	Н	Н	Н	L	L	*	*	*	FC0000h~FCFFFh	7E0000h~7E7FFh
	BA260	Н	Н	Н	Н	Н	Н	L	Н	*	*	*	FD0000h~FDFFFh	7E8000h~7EFFFFh
	BA261	Н	Н	Н	Н	Н	Н	Н	L	*	*	*	FE0000h~FEFFFh	7F0000h~7F7FFFh
	BA262	Н	Н	Н	Н	Н	Н	Н	Н	*	*	*	FF0000h~FFFFFh	7F8000h~7FFFFh



BLOCK SIZE TABLE

(1) TC58FVM7T2A (top boot block)

BLOCK	BLOC	K SIZE	BANK	BAN	BLOCK		
#	BYTE MODE	WORD MODE	#	BYTE MODE	WORD MODE	COUNT	
BA0~BA31	64 Kbytes	32 Kwords	BK0	2048 Kbytes	1024 Kwords	32	
BA32~BA127	64 Kbytes	32 Kwords	BK1	6144 Kbytes	3072 Kwords	96	
BA128~BA223	64 Kbytes	32 Kwords	BK2	6144 Kbytes	3072 Kwords	96	
BA224~BA254	64 Kbytes	32 Kwords	BK3	1984 Kbytes	992 Kwords	31	
BA255~BA262	8 Kbytes	4 Kwords	BK3	64 Kbytes	32 Kwords	8	

(2) TC58FVM7B2A (bottom boot block)

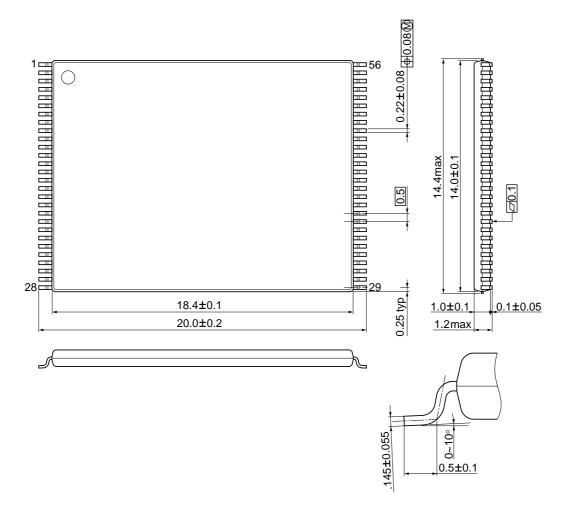
BLOCK	BLOC	K SIZE	BANK	BANK	BLOCK COUNT		
#	BYTE MODE WORD MODE		#	BYTE MODE	WORD MODE	BLOCK COUNT	
BA0~BA7	8 Kbytes	4 Kwords	BK0	64 Kbytes	32 Kwords	8	
BA8~BA38	64 Kbytes	32 Kwords	BK0	1984 Kbytes	992 Kwords	31	
BA39~BA134	64 Kbytes	32 Kwords	BK1	6144 Kbytes	3072 Kwords	96	
BA135~BA230	64 Kbytes	32 Kwords	BK2	6144 Kbytes	3072 Kwords	96	
BA231~BA262	64 Kbytes	32 Kwords	BK3	2048 Kbytes	1024 Kwords	32	



PACKAGE DIMENSION

Unit: mm

TSOPI56-P-1420-0.50





Revision History

Date	Version	Description
2002-3-14	1.00	Original version
2002-5-14	1.01	Top Boot Address (refine). (54page)
2002-5-29	1.02	Added speed version.
2002-6-11	1.03	Changed t _{SUSP} spec. (23page) Added a timing diagram of read after CFI/HROM command input. (26page)
2002-7-30	1.04	Erase Hold Time. (23page) Pin Capacitance. (19page) Annotated VID/VACC. (19page) Added spec of IDDO8 (1page, 20 page) Changed comment of IDDO1/IDDO7 (1page, 20page)
2002-8-30	1.05	Added typically spec of DC (21page)
2002-10-21	1.06	Added ordering information (page2)
2002-10-24	1.07	Generalize
2003-01-29	1.08	Revised the PIN Capacitance. Added the Block protect 2 at mode selection. Added a part of comment (CMD ID-READ). Modified the comment of Hidden ROM Area. Modified the name of Package dimension. Modified the absolute maximum range of Power Dissipation. Deleted the spec of t _{AHW} . Modified the block address table. Annotated Absolute Maximum Ratings. Deleted annotation of Recommended DC operating conditions.

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